Async/Page/Burst CellularRAM® 1.0 Memory

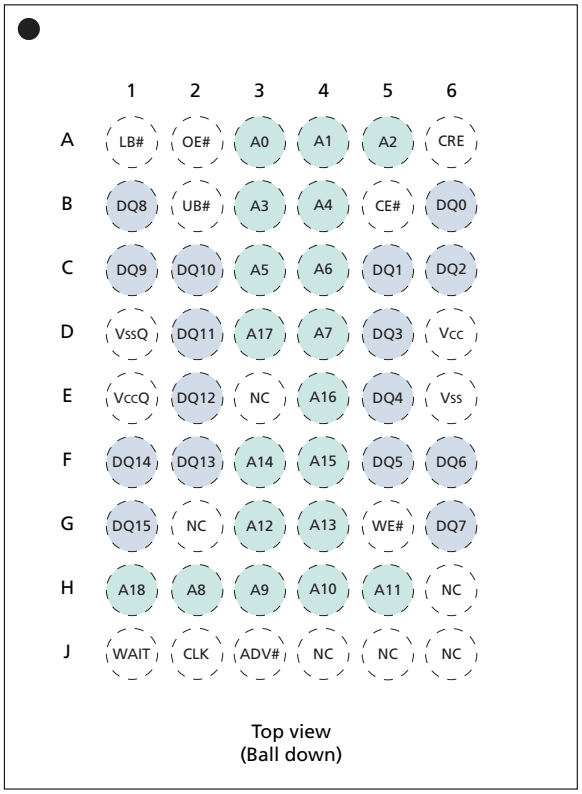
MT45W512KW16BEGB

Features

- Single device supports asynchronous, page, and burst operations
- Random access time: 70ns
- VCC, VCCQ voltages
  - 1.7–1.95V VCC
  - 1.7–3.6V[1] VCCQ
- Page mode read access
  - 16-word page size
  - Interpage read access: 70ns
  - Intrapage read access: 20ns
- Burst mode write access: continuous burst
- Burst mode read access
  - 4, 8, or 16 words or continuous burst
  - MAX clock rate: 104 MHz (^{t}CLK = 9.62ns)
  - Burst initial latency: 38.5ns (4 clocks) at 104 MHz
  - ^{t}ACLK: 7ns at 104 MHz
- Low power consumption
  - Asynchronous read: <20mA
  - Intrapage read: <15mA
  - Intrapage read initial access, burst read: (38.5ns [4 clocks] at 104 MHz) <35mA
  - Continuous burst read: <28mA
  - Standby: <65µA
  - Deep power-down (DPD): <10µA (TYP at 25°C)
- Low-power features
  - Partial-array refresh (PAR)
  - DPD mode

Options	Designator
• Configuration	
– 512K x 16	MT45W512KW16BE
• Package	
– 54-ball VFBGA (“green”)	GB
• Access time	
– 70ns	-70
• Frequency	
– 80 MHz	8
– 104 MHz	1
• Standby power	
– Standard	None

Figure 1: 54-Ball VFBGA Ball Assignment



Options (continued)	Designator
• Operating temperature range	
– Wireless (–30°C to +85°C)[1]	WT
– Industrial (–40°C to +85°C)[2]	IT

Notes: 1. The 3.6V I/O and the –30°C wireless temperature exceed the CellularRAM Workgroup 1.0 specification.
2. Contact factory for availability.

Part Number Example:

MT45W512KW16BEGB-701WT

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General Description

Micron® CellularRAM® is a high-speed, CMOS PSRAM memory developed for low-power, portable applications. The MT45W512KW16BEGB is an 8Mb DRAM core device organized as 512K x 16 bits. This device includes an industry-standard burst mode Flash interface that dramatically increases read/write bandwidth compared with other low-power SRAM or pseudo-SRAM (PSRAM) offerings.

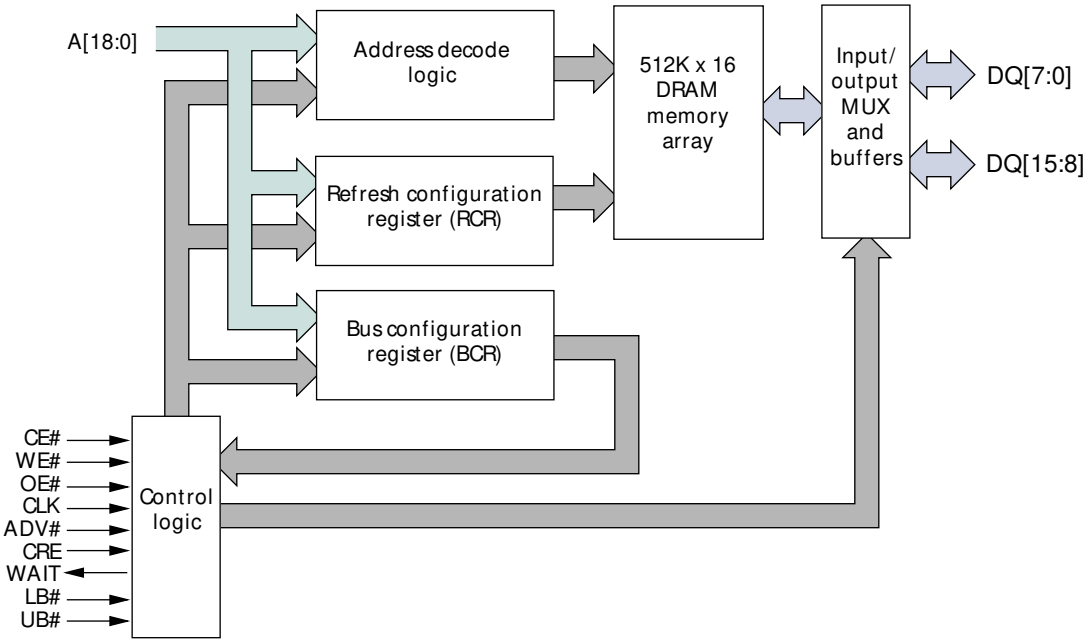
For seamless operation on a burst Flash bus, CellularRAM products incorporate a transparent self refresh mechanism. The hidden refresh requires no additional support from the system memory controller and has no significant impact on device read/write performance.

Two user-accessible control registers define device operation. The bus configuration register (BCR) defines how the CellularRAM device interacts with the system memory bus and is nearly identical to its counterpart on burst mode Flash devices. The refresh configuration register (RCR) is used to control how refresh is performed on the DRAM array. These registers are automatically loaded with default settings during power-up and can be updated anytime during normal operation.

Special attention has been focused on standby current consumption during self refresh. This CellularRAM product includes two system-accessible mechanisms to minimize standby current. Partial-array refresh (PAR) limits refresh to only that part of the DRAM array that contains essential data. Deep power-down (DPD) halts the REFRESH operation altogether and is used when no vital information is stored in the device. These two refresh mechanisms are accessed through the RCR.

Functional Block Diagrams

Figure 2: Functional Block Diagram (512K x 16)



Note: Functional block diagrams illustrate simplified device operation. See the ball description table and timing diagrams for detailed information.

Ball Descriptions

Table 1: VFBGA Ball Descriptions

VFBGA Assignment	Symbol	Type	Description
H1, D3, E4, F4, F3, G4, G3, H5, H4, H3, H2, D4, C4, C3, B4, B3, A5, A4, A3	A[18:0]	Input	**Address inputs**: Inputs for addresses during READ and WRITE operations. Addresses are internally latched during READ and WRITE cycles. The address lines are also used to define the value to be loaded into the BCR or the RCR.
J2	CLK	Input	**Clock**: Synchronizes the memory to the system operating frequency during synchronous operations. When configured for synchronous operation, the address is latched on the first rising CLK edge when ADV# is active. CLK is static LOW or HIGH during asynchronous access READ and WRITE operations and during PAGE READ ACCESS operations.
J3	ADV#	Input	**Address valid**: Indicates that a valid address is present on the address inputs. Addresses can be latched on the rising edge of ADV# during asynchronous READ and WRITE operations. ADV# can be held LOW during asynchronous READ and WRITE operations.
A6	CRE	Input	**Configuration register enable**: When CRE is HIGH, WRITE operations load the RCR or BCR.
B5	CE#	Input	**Chip enable**: Activates the device when LOW. When CE# is HIGH, the device is disabled and goes into standby or DPD mode.
A2	OE#	Input	**Output enable**: Enables the output buffers when LOW. When OE# is HIGH, the output buffers are disabled.
G5	WE#	Input	**Write enable**: Determines whether a given cycle is a WRITE cycle. If WE# is LOW, the cycle is a WRITE either to a configuration register or to the memory array.
A1	LB#	Input	**Lower byte enable**: DQ[7:0].
B2	UB#	Input	**Upper byte enable**: DQ[15:8].
G1, F1, F2, E2, D2, C2, C1, B1, G6, F6, F5, E5, D5, C6, C5, B6	DQ[15:0]	Input/ Output	Data inputs/outputs.
J1	WAIT	Output	**Wait**: Provides data-valid feedback during burst READ and WRITE operations. The signal is gated by CE#. WAIT is used to arbitrate collisions between REFRESH and READ/WRITE operations. WAIT is asserted when a burst crosses a row boundary. WAIT is also used to mask the delay associated with opening a new internal page. WAIT is asserted and should be ignored during asynchronous and page mode operations. WAIT is High-Z when CE# is HIGH.
D6	V_{CC}	Supply	**Device power supply (1.7–1.95V)**: Power supply for device core operation.
E1	V_{CCQ}	Supply	**I/O power supply (1.7–3.6V)**: Power supply for input/output buffers.
E6	V_{SS}	Supply	V_{SS} must be connected to ground.
D1	V_{SSQ}	Supply	V_{SSQ} must be connected to ground.
E3, G2, H6, J4, J5, J6	NC	–	Not internally connected.

Note: The CLK and ADV# inputs can be tied to V_{SS} if the device is always operating in asynchronous or page mode. WAIT will be asserted, but should be ignored during asynchronous and page mode operations.

Bus Operations

Table 2: Bus Operations: Asynchronous Mode

Mode	Power	CLK[1]	ADV#	CE#	OE#	WE#	CRE	LB#/ UB#	WAIT[2]	DQ[15:0][3]	Notes
READ	Active	L	L	L	L	H	L	L	Low-Z	Data-out	4
WRITE	Active	L	L	L	X	L	L	L	Low-Z	Data-in	4
Standby	Standby	L	X	H	X	X	L	X	High-Z	High-Z	5, 6
No operation	Idle	L	X	L	X	X	L	X	Low-Z	X	4, 6
Configuration register WRITE	Active	L	L	L	H	L	H	X	Low-Z	High-Z	
Configuration register READ	Active	L	L	L	H	H	H	X	Low-Z	Configuration register out	7
DPD	Deep power-down	L	X	H	X	X	X	X	High-Z	High-Z	8

Notes:
1. CLK must be static HIGH or LOW during asynchronous READ and asynchronous WRITE modes and to achieve standby power during standby and DPD modes. CLK must be static (HIGH or LOW) during burst suspend.
2. The WAIT polarity is configured through the bus configuration register (BCR[10]).
3. When LB# and UB# are in select mode (LOW), DQ[15:0] are affected. When only LB# is in select mode, DQ[7:0] are affected. When only UB# is in the select mode, DQ[15:8] are affected.
4. The device will consume active power in this mode whenever addresses are changed.
5. When the device is in standby mode, address inputs and data inputs/outputs are internally isolated from any external influence.
6. V_{IN} = V_{CCQ} or 0V; all device balls must be static (unswitched) to achieve standby current.
7. This device supports CRE-controlled configuration register READS. This feature is not an official CellularRAM 1.0 feature.
8. DPD is maintained until RCR is reconfigured.

Table 3: Bus Operations: Burst Mode

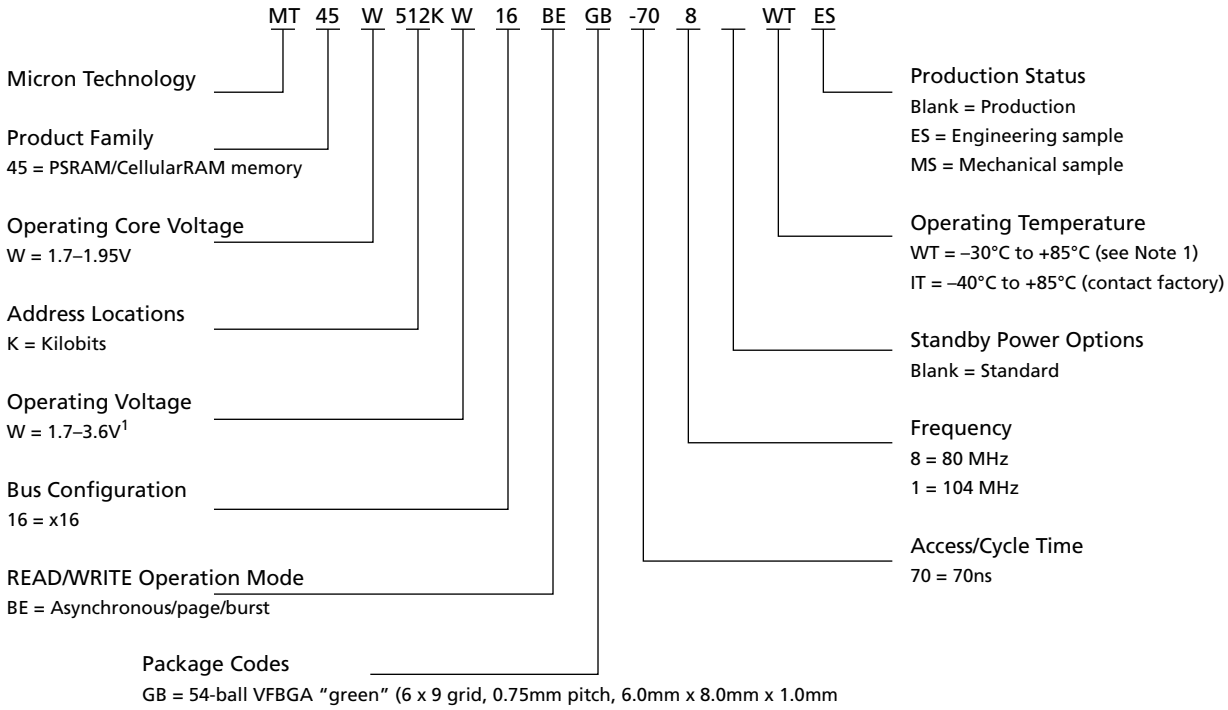
Mode	Power	CLK[1]	ADV#	CE#	OE#	WE#	CRE	LB#/ UB#	WAIT[2]	DQ[15:0][3]	Notes
Asynchronous READ	Active	L	L	L	L	H	L	L	Low-Z	Data-out	4
Asynchronous WRITE	Active	L	L	L	X	L	L	L	Low-Z	Data-in	4
Standby	Standby	L	X	H	X	X	L	X	High-Z	High-Z	5, 6
No operation	Idle	L	X	L	X	X	L	X	Low-Z	X	4, 6
Initial burst READ	Active	⎍	L	L	X	H	L	L	Low-Z	X	4, 7
Initial burst WRITE	Active	⎍	L	L	H	L	L	X	Low-Z	X	4, 7
Burst continue	Active	⎍	H	L	X	X	X	L	Low-Z	Data-in or data-out	4, 7
Burst suspend	Active	X	X	L	H	X	L	X	Low-Z	High-Z	4, 7
Configuration register WRITE	Active	⎍	L	L	H	L	H	X	Low-Z	High-Z	7
Configuration register READ	Active	⎍	L	L	H	H	H	X	Low-Z	Configuration register out	7, 8
DPD	Deep power-down	L	X	H	X	X	X	X	High-Z	High-Z	9

Notes:
1. CLK must be static HIGH or LOW during asynchronous READ and asynchronous WRITE modes and to achieve standby power during standby and DPD modes. CLK must be static (HIGH or LOW) during burst suspend.
2. The WAIT polarity is configured through the bus configuration register (BCR[10]).
3. When LB# and UB# are in select mode (LOW), DQ[15:0] are affected. When only LB# is in select mode, DQ[7:0] are affected. When only UB# is in the select mode, DQ[15:8] are affected.
4. The device will consume active power in this mode whenever addresses are changed.
5. When the device is in standby mode, address inputs and data inputs/outputs are internally isolated from any external influence.
6. V_{IN} = V_{CCQ} or 0V; all device balls must be static (unswitched) to achieve standby current.
7. Burst mode operation is initialized through the bus configuration register (BCR[15]).
8. This device supports CRE-controlled configuration register READS. This feature is not an official CellularRAM 1.0 feature.
9. DPD is maintained until RCR is reconfigured.

Part Numbering Information

Micron CellularRAM devices are available in several different configurations and densities (see Figure 3).

Figure 3: Part Number Chart



Notes: 1. The 3.6V I/O and the –30°C wireless temperature exceed the CellularRAM Workgroup 1.0 specification.

Valid Part Number Combinations

After building the part number using the part numbering chart, visit the Micron Web site at www.micron.com/psram to verify that the part number is offered and valid. If the device required is not on this list, contact the factory.

Device Marking

Due to the size of the package, the Micron-standard part number is not printed on the top of the device. Instead, an abbreviated device mark consisting of a five-digit alphanumeric code is used. The abbreviated device marks are cross-referenced to the Micron part numbers at the FBGA Part Marking Decoder site, www.micron.com/decoder. To find how to locate the abbreviated mark on the device, refer to customer service note CSN-11, "Product Mark/Label," at www.micron.com/csn.

Functional Description

In general, MT45W512KW16BEGB devices are high-density alternatives to SRAM and PSRAM products, popular in low-power, portable applications.

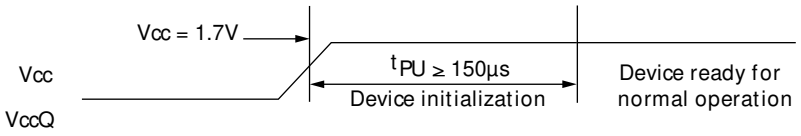
The MT45W512KW16BEGB contains an 8,388,608-bit DRAM core organized as 524,288 addresses by 16 bits. This device implements the same high-speed bus interface found on burst mode Flash products.

The CellularRAM bus interface supports both asynchronous and burst mode transfers. Page mode accesses are also included as a bandwidth-enhancing extension to the asynchronous READ protocol.

Power-Up Initialization

CellularRAM products include an on-chip voltage sensor used to launch the power-up initialization process. Initialization will configure the BCR and the RCR with their default settings (see Figure 19 on page 24 and Figure 24 on page 28). VCC and VCCQ must be applied simultaneously. When VCC and VCCQ reach a stable level at or above 1.7V, the device will require 150µs to complete its self-initialization process. During the initialization period, CE# should remain HIGH. When initialization is complete, the device is ready for normal operation.

Figure 4: Power-Up Initialization Timing



Bus Operating Modes

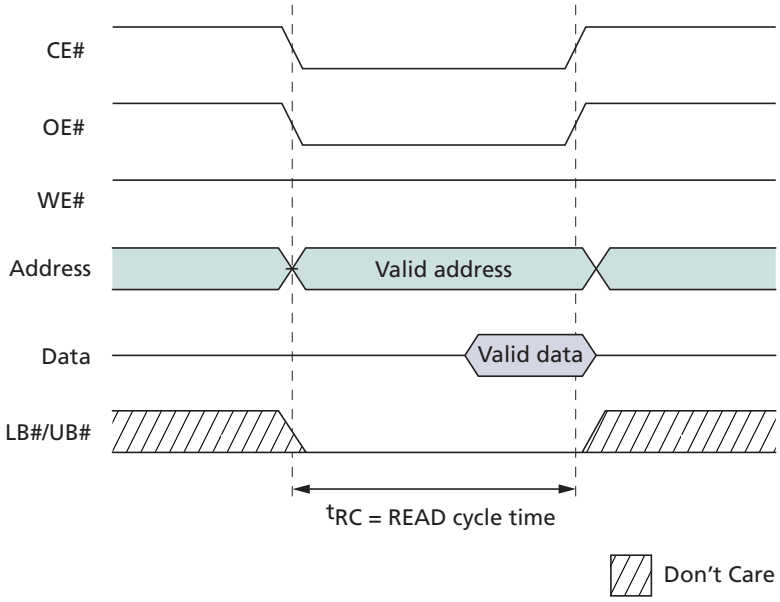
The MT45W512KW16BEGB CellularRAM products incorporate a burst mode interface found on Flash products targeting low-power, wireless applications. This bus interface supports asynchronous, page mode, and burst mode READ and WRITE transfers. The specific interface supported is defined by the value loaded into the BCR. Page mode is controlled by the refresh configuration register (RCR[7]).

Asynchronous Mode

CellularRAM products power up in the asynchronous operating mode. This mode uses the industry-standard SRAM control bus (CE#, OE#, WE#, LB#/UB#). READ operations (Figure 5 on page 11) are initiated by bringing CE#, OE#, and LB#/UB# LOW while keeping WE# HIGH. Valid data will be driven out of the I/Os after the specified access time has elapsed. WRITE operations (Figure 6 on page 11) occur when CE#, WE#, and LB#/UB# are driven LOW. During asynchronous WRITE operations, the OE# level is a "Don't Care," and WE# will override OE#. The data to be written is latched on the rising edge of CE#, WE#, or LB#/UB#, whichever occurs first. Asynchronous operations (page mode disabled) either can use the ADV input to latch the address, or can drive ADV LOW during the entire READ/WRITE operation.

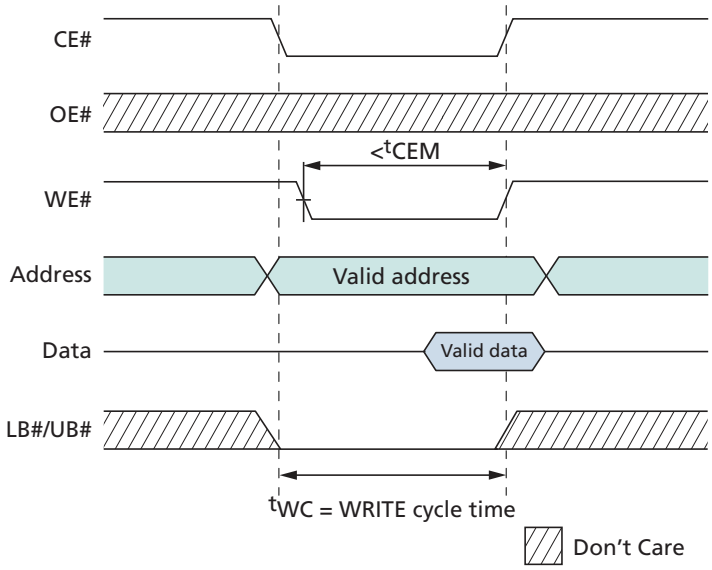
During asynchronous operation, the CLK input must be held static LOW or HIGH. WAIT will be driven while the device is enabled, and its state should be ignored. WE# LOW time must be limited to ^{t}CEM.

Figure 5: READ Operation (ADV = LOW)



Note: ADV must remain LOW for page mode operation.

Figure 6: WRITE Operation (ADV = LOW)



Page Mode READ Operation

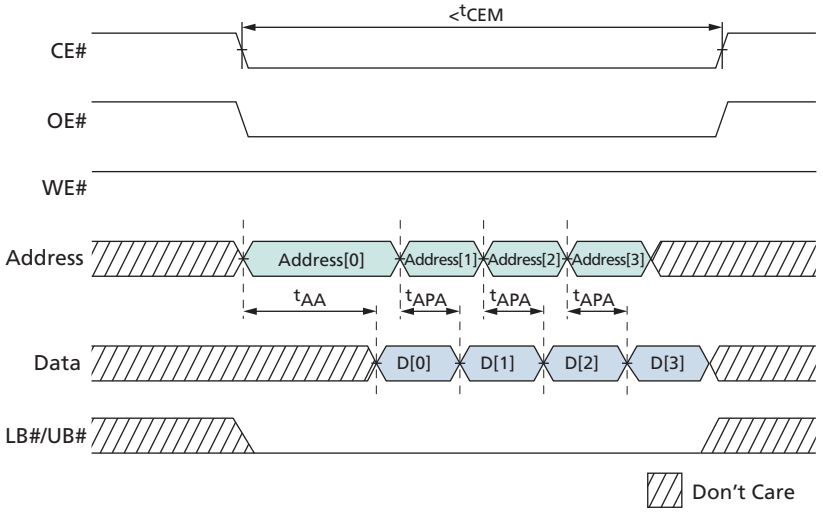
Page mode is a performance-enhancing extension to the legacy asynchronous READ operation. In page-mode-capable products, an initial asynchronous READ access is performed, and then adjacent addresses can be read quickly by simply changing the low-order address. Addresses A[3:0] are used to determine the members of the 16-address CellularRAM page. Any change in addresses A[4] or higher will initiate a new ^{t}AA access time. Figure 7 on page 12 shows the timing for a page mode access.

Page mode takes advantage of the fact that adjacent addresses can be read in a shorter period of time than random addresses. WRITE operations do not include comparable page mode functionality.

During asynchronous page mode operation, the CLK input must be held static LOW or HIGH. CE# must be driven HIGH upon completion of a page mode access. WAIT will be driven while the device is enabled, and its state should be ignored. Page mode is enabled by setting RCR[7] to HIGH. ADV must be driven LOW during all page mode READ accesses.

The CE# LOW time is limited by refresh considerations. CE# must not stay LOW longer than ^{t}CEM.

Figure 7: Page Mode READ Operation (ADV = LOW)



Burst Mode Operation

Burst mode operations enable high-speed synchronous READ and WRITE operations. Burst operations consist of a multiclock sequence that must be performed in an ordered fashion. After CE# goes LOW, the address to access is latched on the next rising edge of CLK that ADV# is LOW. During this first clock rising edge, WE# indicates whether the operation is going to be a READ (WE# = HIGH, Figure 8 on page 13) or a WRITE (WE# = LOW, Figure 9 on page 14).

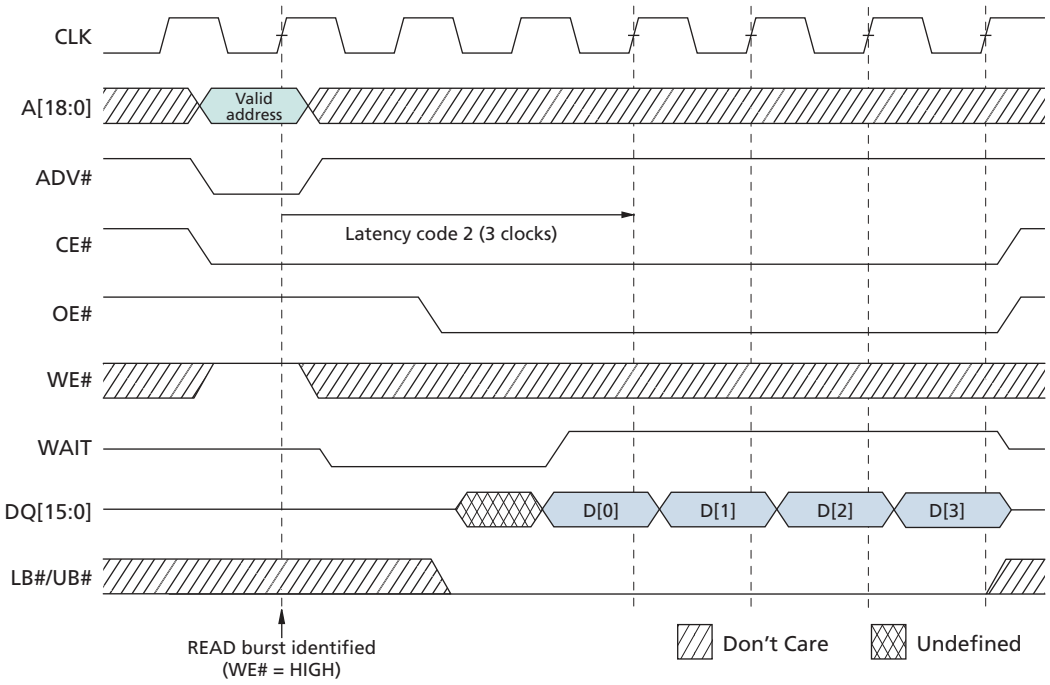
The size of a burst can be specified in the BCR as either fixed-length or continuous. Fixed-length bursts consist of 4, 8, or 16 words. Continuous bursts have the ability to start at a specified address and burst through the entire memory. The latency count stored in the BCR defines the number of clock cycles that elapse before the initial data value is transferred between the processor and CellularRAM device.

The WAIT output will be asserted as soon as CE# goes LOW and will be deasserted to indicate when data is to be transferred into or out of the memory. WAIT will again be asserted if the burst crosses the boundary between 128-word rows. When the CellularRAM device has restored the previous row's data and accessed the next row, WAIT will be de-asserted and the burst can continue (see Figure 35 on page 43).

By suspending burst mode, the processor can access other devices without incurring the timing penalty of the initial latency for a new burst. Bursts are suspended by stopping CLK. CLK can be stopped HIGH or LOW. If another device will use the data bus while the burst is suspended, OE# should be taken HIGH to disable the CellularRAM outputs; otherwise, OE# can remain LOW. Note that the WAIT output will continue to be active, and, as a result, no other devices should directly share the WAIT connection to the controller. To continue the burst sequence, OE# is taken LOW, and then CLK is restarted after valid data is available on the bus.

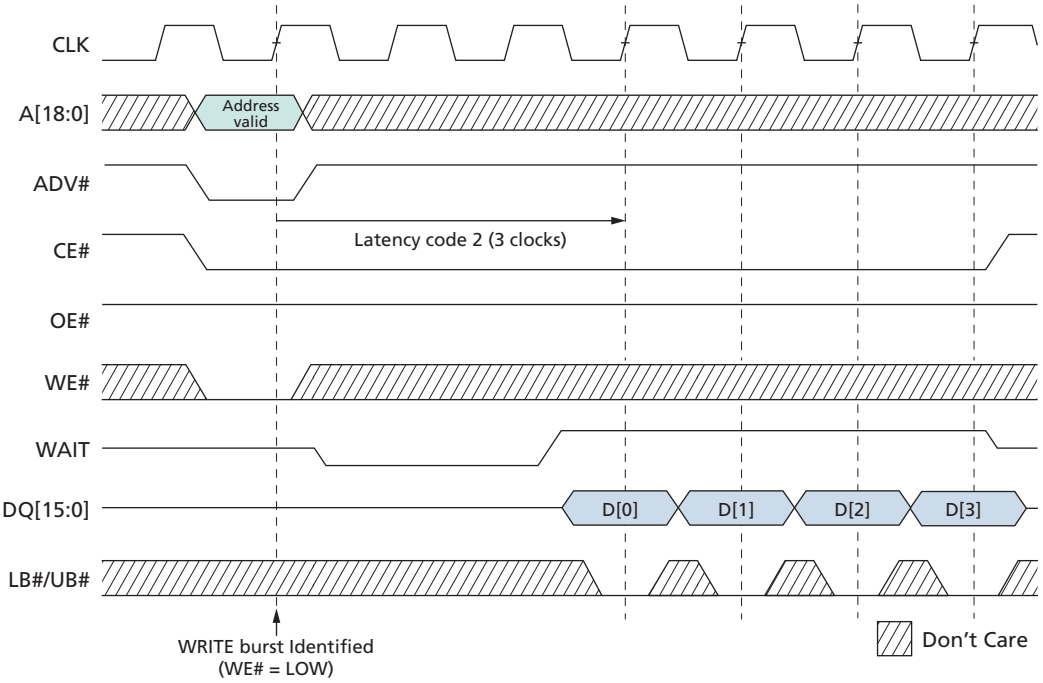
The CE# LOW time is limited by refresh considerations. CE# must not stay LOW longer than ^{t}CEM unless row boundaries are crossed at least every ^{t}CEM. If a burst suspension will cause CE# to remain LOW for longer than ^{t}CEM, CE# should be taken HIGH and the burst restarted with a new CE# LOW/ ADV# LOW cycle.

Figure 8: Burst Mode READ (4-Word Burst)



Note: Nondefault BCR settings: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Figure 9: Burst Mode WRITE (4-Word Burst)



Note: Nondefault BCR settings: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

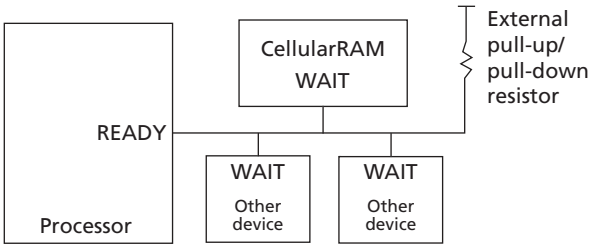
Mixed-Mode Operation

The device can support a combination of synchronous READ and asynchronous WRITE operations when the BCR is configured for synchronous operation. The asynchronous WRITE operation requires that the clock (CLK) be held static LOW or HIGH during the entire sequence. The ADV# signal can be used to latch the target address, or it can remain LOW during the entire WRITE operation. CE# must return HIGH when transitioning between mixed-mode operations. Note that the ^{t}CKA period is the same as a READ or WRITE cycle. This time is required to ensure adequate refresh. Mixed-mode operation facilitates a seamless interface to legacy burst mode Flash memory controllers (see Figure 43 on page 51).

WAIT Operation

The WAIT output on a CellularRAM device is typically connected to a shared, system-level WAIT signal (see Figure 10). The shared WAIT signal is used by the processor to coordinate transactions with multiple memories on the synchronous bus.

Figure 10: Wired-OR WAIT Configuration



After a READ or WRITE operation has been initiated, WAIT goes active to indicate that the CellularRAM device requires additional time before data can be transferred. For READ operations, WAIT will remain active until valid data is output from the device. For WRITE operations, WAIT will indicate to the memory controller when data will be accepted into the CellularRAM device. When WAIT transitions to an inactive state, the data burst will progress on successive clock edges.

During a burst cycle, CE# must remain asserted until the first data is valid. Bringing CE# HIGH during this initial latency may cause data corruption.

The WAIT output also performs an arbitration role when a READ or WRITE operation is launched while an on-chip refresh is in progress. If a collision occurs, WAIT is asserted for additional clock cycles until the refresh has completed (see Figure 11 on page 16 and Figure 12 on page 16). When the refresh operation has completed, the READ or WRITE operation will continue normally.

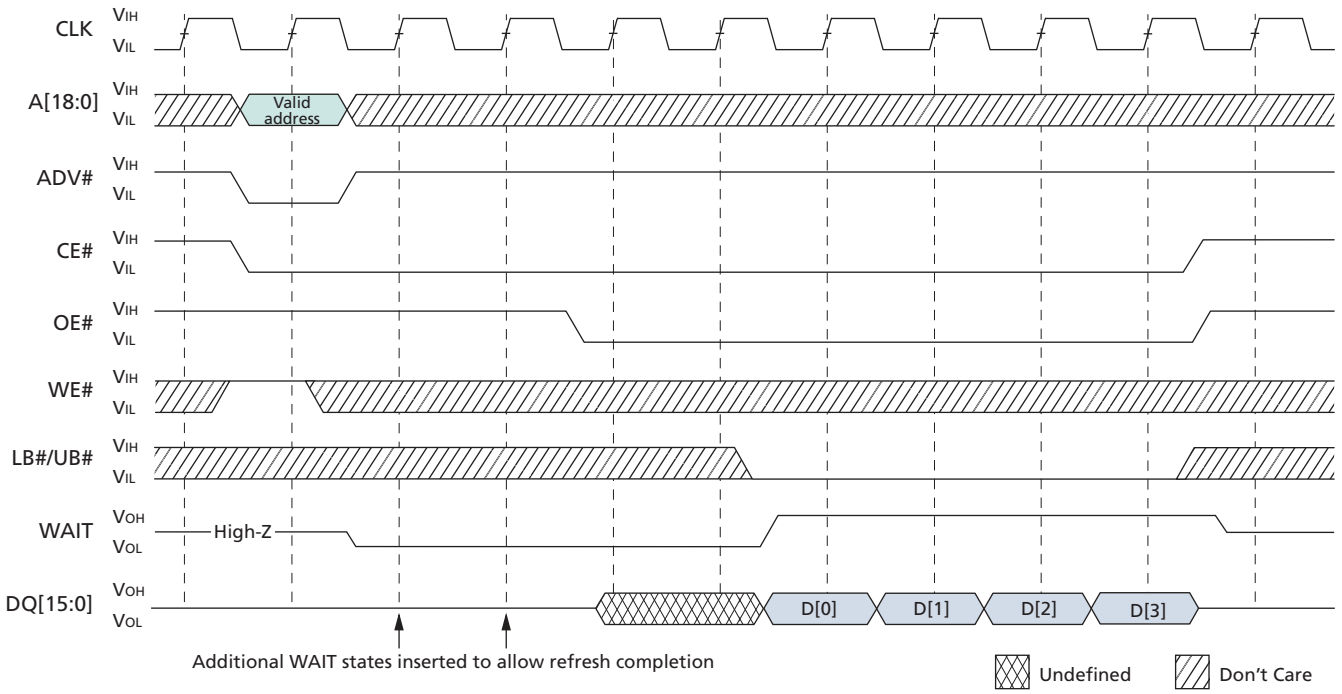
WAIT is also asserted when a continuous READ or WRITE burst crosses a row boundary. The WAIT assertion allows time for the new row to be accessed and permits any pending REFRESH operations to be performed.

LB#/UB# Operation

The LB# enable and UB# enable signals support byte-wide data transfers. During READ operations, the enabled byte(s) are driven onto the DQ. The DQ associated with a disabled byte are put into a High-Z state during a READ operation. During WRITE operations, any disabled bytes will not be transferred to the RAM array, and the internal value will remain unchanged. During an asynchronous WRITE cycle, the data to be written is latched on the rising edge of CE#, WE#, LB#, or UB#, whichever occurs first.

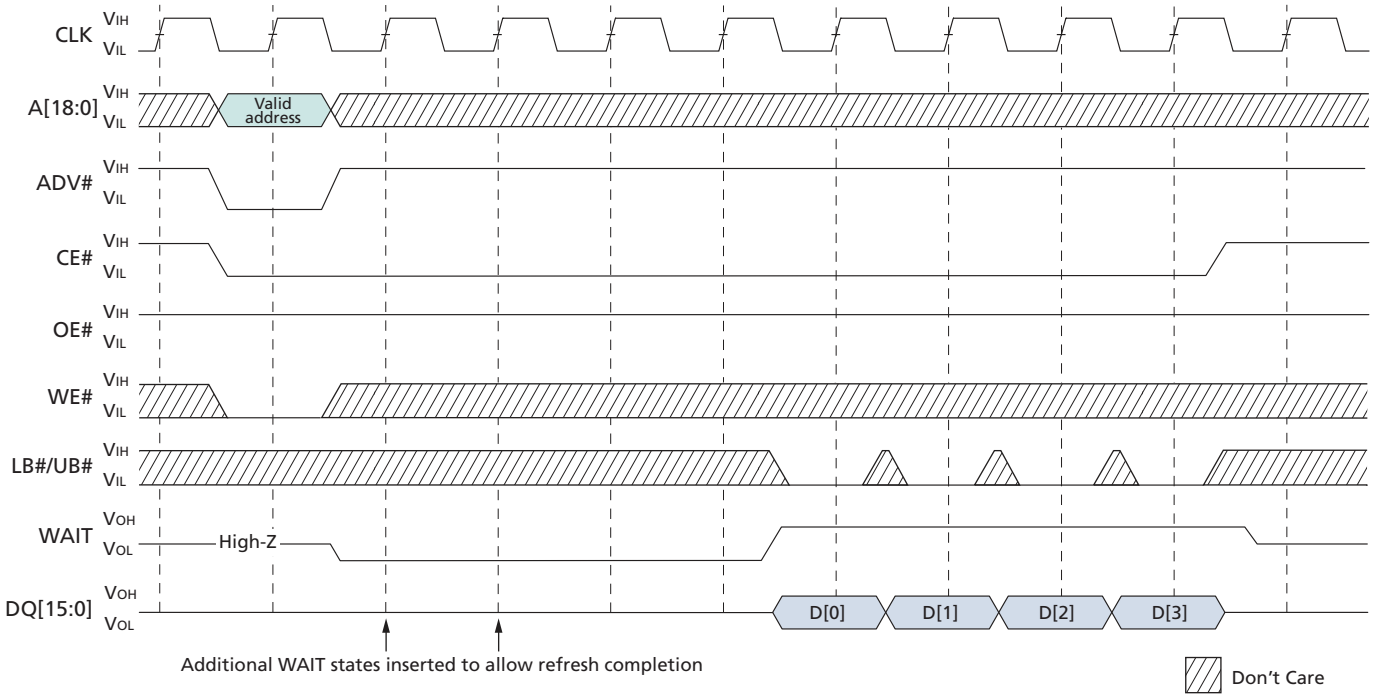
When both the LB# and UB# are disabled (HIGH) during an operation, the device will disable the data bus from receiving or transmitting data. Although the device will seem to be deselected, it remains in an active mode as long as CE# remains LOW.

Figure 11: Refresh Collision During READ Operation



Note: Nondefault BCR settings: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Figure 12: Refresh Collision During WRITE Operation



Note: Nondefault BCR settings: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Low-Power Operation

Standby Mode Operation

During standby, the device current consumption is reduced to the level necessary to perform the DRAM REFRESH operation. Standby operation occurs when CE# is HIGH.

The device will enter a reduced power state upon completion of a READ or WRITE operation or when the address and control inputs remain static for an extended period of time. This mode will continue until a change occurs to the address or control inputs.

Deep Power-Down Operation

Deep power-down (DPD) operation disables all refresh-related activity. This mode is used if the system does not require the storage provided by the CellularRAM device. Any stored data will become corrupted when DPD is enabled. When refresh activity has been reenabled by rewriting the RCR, the CellularRAM device will require 150µs to perform an initialization procedure before normal operations can resume. During this 150µs period, the current consumption will be higher than the specified standby levels, but considerably lower than the active current specification.

DPD cannot be enabled or disabled by writing to the RCR using the software-access sequence; instead, the RCR should be accessed using CRE.

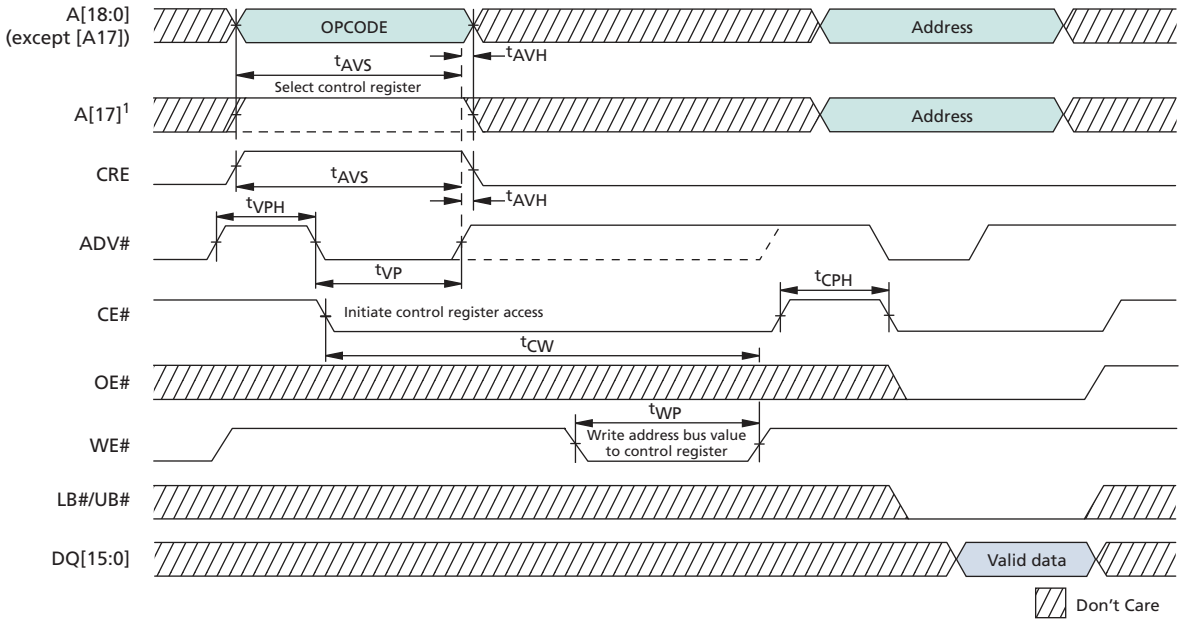
Configuration Registers

Two user-accessible configuration registers define the device operation. The bus configuration register (BCR) defines how the CellularRAM interacts with the system memory bus and is nearly identical to its counterpart on burst mode Flash devices. The refresh configuration register (RCR) is used to control how refresh is performed on the DRAM array. These registers are automatically loaded with default settings during power-up and can be updated any time the devices are operating in a standby state.

Access Using CRE

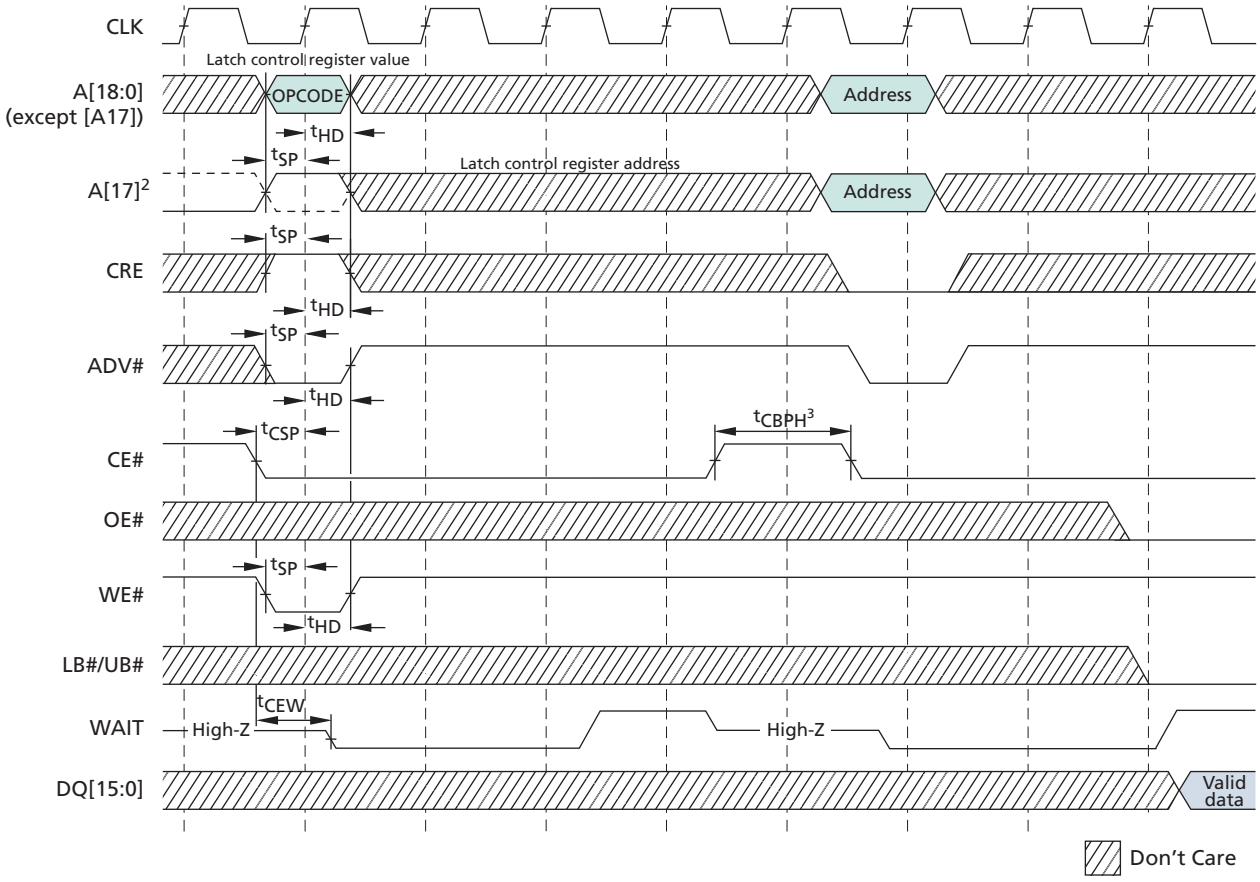
The configuration registers are loaded either using a synchronous or an asynchronous WRITE operation when the configuration register enable (CRE) input is HIGH (see Figure 13 on page 18 and Figure 14 on page 19). When CRE is LOW, a READ or WRITE operation will access the memory array. The register values are placed on address pins A[18:0]. In an asynchronous WRITE, the values are latched into the configuration register on the rising edge of ADV#, CE#, or WE#, whichever occurs first; LB# and UB# are "Don't Care." The BCR is accessed when A[17] is HIGH; the RCR is accessed when A[17] is LOW. For READs, address inputs other than A17 are "Don't Care," and register bits 15:0 are output on DQ[15:0].

Figure 13: Asynchronous Mode Configuration Register Write Followed by READ ARRAY Operation



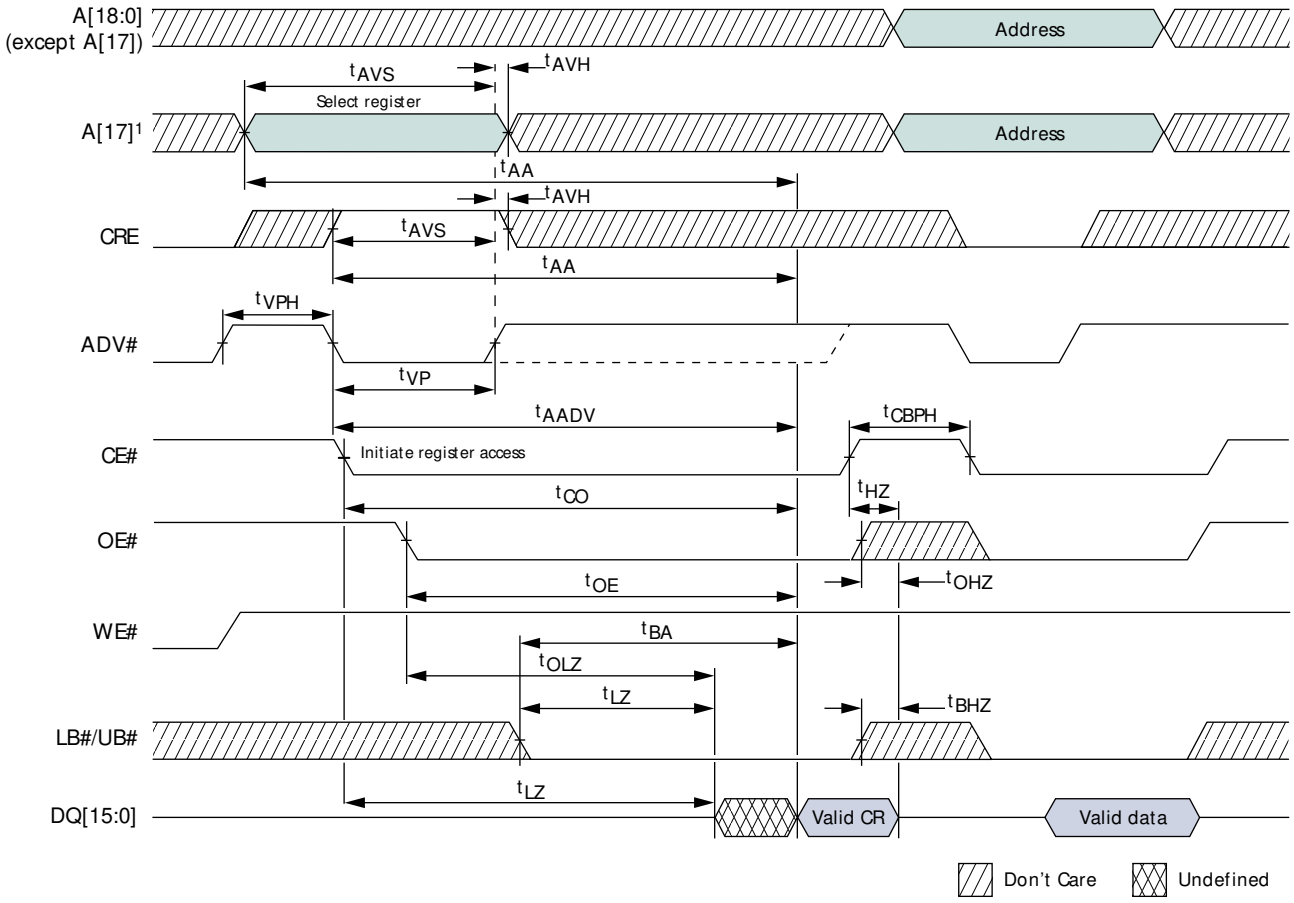
Notes: 1. A[17] = LOW to load RCR; A[17] = HIGH to load BCR.

Figure 14: Synchronous Mode Configuration Register WRITE Followed by READ ARRAY Operation



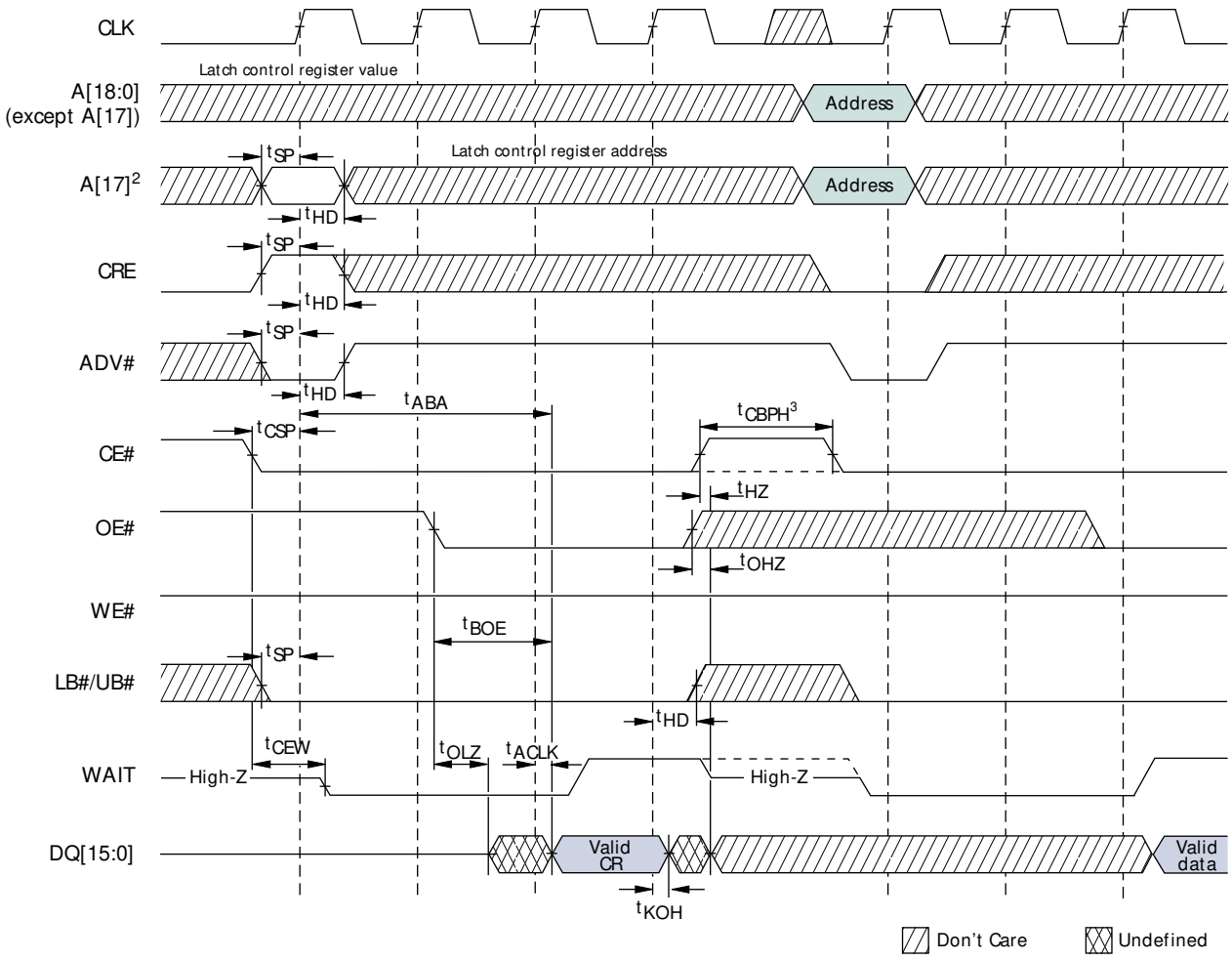
Notes:
1. Nondefault BCR settings for CR WRITE in synchronous mode followed by READ ARRAY operation: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. A[17] = LOW to load RCR; A[17] = HIGH to load BCR.
3. CE# must remain LOW to complete a burst-of-one WRITE. WAIT must be monitored—additional WAIT cycles caused by refresh collisions require a corresponding number of additional CE# LOW cycles.

Figure 15: Asynchronous Mode Configuration Register READ Followed by READ ARRAY Operation



Notes: 1. A[17] = LOW to load RCR; A[17] = HIGH to load BCR.

Figure 16: Synchronous Mode Configuration Register READ Followed by READ ARRAY Operation



Notes:
1. Nondefault BCR settings for synchronous mode register READ followed by READ ARRAY operation: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. A[17] = LOW to load RCR; A[17] = HIGH to load BCR.
3. CE# must remain LOW to complete a burst-of-one READ. WAIT must be monitored—additional WAIT cycles caused by refresh collisions require a corresponding number of additional CE# LOW cycles.

Software Access to the Configuration Register

Software access of the configuration registers uses a sequence of asynchronous READ and asynchronous WRITE operations. The contents of the configuration registers can be read or modified using the software sequence.

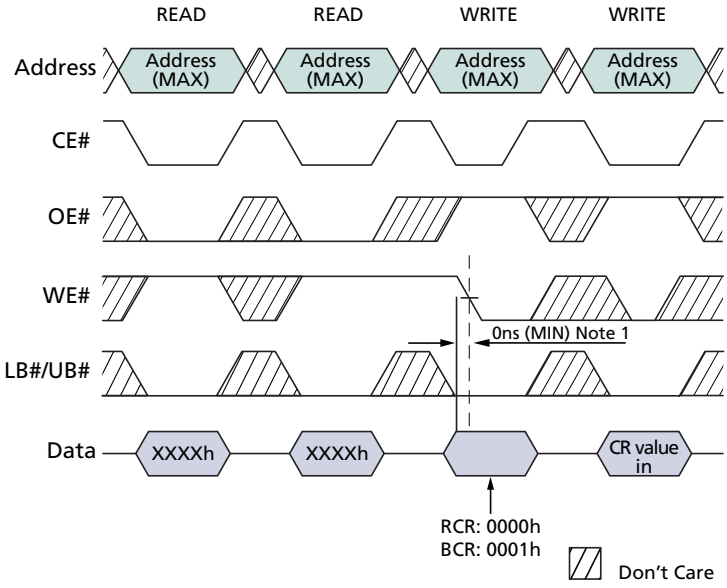
The configuration registers are loaded using a four-step sequence consisting of two asynchronous READ operations followed by two asynchronous WRITE operations (see Figure 17). The read sequence is virtually identical except that an asynchronous READ is performed during the fourth operation (see Figure 18 on page 23). Note that a third READ cycle of the highest address will cancel the access sequence until a different address is read.

The address used during all READ and WRITE operations is the highest address of the CellularRAM device being accessed (7FFFFh); the content at this address is not changed by using this sequence.

The data value presented during the third operation (WRITE) in the sequence defines whether the BCR or the RCR is to be accessed. If the data is 0000h, the sequence will access the RCR; if the data is 0001h, the sequence will access the BCR. During the fourth operation, DQ[15:0] transfer data into or out of bits 15–0 of the configuration registers.

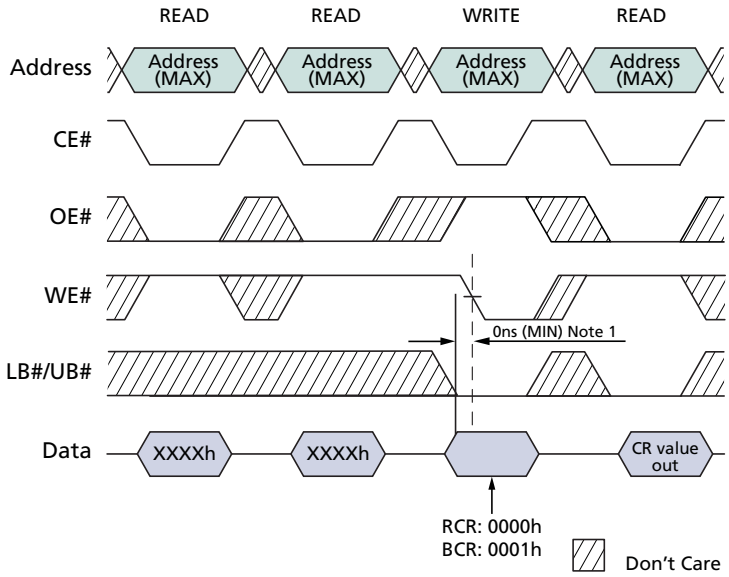
The use of the software sequence does not affect the ability to perform the standard (CRE-controlled) method of loading the configuration registers. However, the software nature of this access mechanism eliminates the need for the control register enable (CRE) pin. If the software mechanism is used, the CRE pin can simply be tied to VSS. The port line often used for CRE control purposes is no longer required.

Figure 17: Load Configuration Register



Notes: 1. It is possible that the data stored at the highest memory location will be altered if the data at the falling edge of WE# is not 0000h or 0001h.

Figure 18: Read Configuration Register



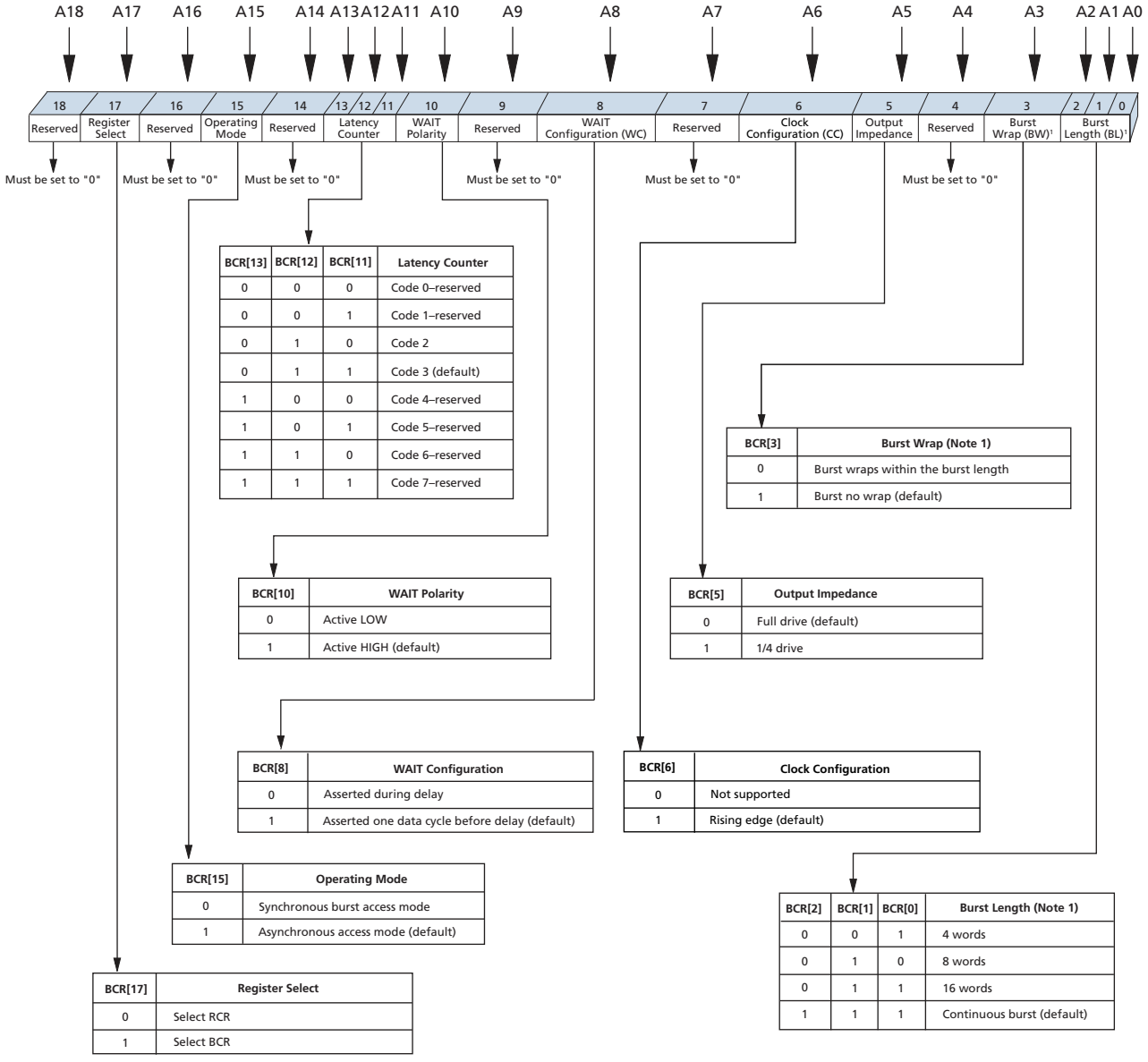
Notes: 1. It is possible that the data stored at the highest memory location will be altered if the data at the falling edge of WE# is not 0000h or 0001h.

Bus Configuration Register

The BCR defines how the CellularRAM device interacts with the system memory bus. Page mode operation is enabled by a bit contained in the RCR. Figure 19 defines the control bits in the BCR. At power-up, the BCR is set to 9D4Fh.

The BCR is accessed using CRE and A[17] HIGH or through the configuration register software sequence with DQ = 0001h on the third cycle.

Figure 19: Bus Configuration Register Definition



Notes: 1. All burst WRITEs are continuous.

Table 4: Sequence and Burst Length

Burst Wrap		Starting Address	4-Word Burst Length	8-Word Burst Length	16-Word Burst Length	Continuous Burst
BCR[3]	Wrap	(Decimal)	Linear	Linear	Linear	Linear
0	Yes	0	0-1-2-3	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7-8-9-10-11-12-13-14-15	0-1-2-3-4-5-6-…
		1	1-2-3-0	1-2-3-4-5-6-7-0	1-2-3-4-5-6-7-8-9-10-11-12-13-14-15-0	1-2-3-4-5-6-7-…
		2	2-3-0-1	2-3-4-5-6-7-0-1	2-3-4-5-6-7-8-9-10-11-12-13-14-15-0-1	2-3-4-5-6-7-8-…
		3	3-0-1-2	3-4-5-6-7-0-1-2	3-4-5-6-7-8-9-10-11-12-13-14-15-0-1-2	3-4-5-6-7-8-9-…
		4		4-5-6-7-0-1-2-3	4-5-6-7-8-9-10-11-12-13-14-15-0-1-2-3	4-5-6-7-8-9-10-…
		5		5-6-7-0-1-2-3-4	5-6-7-8-9-10-11-12-13-14-15-0-1-2-3-4	5-6-7-8-9-10-11-…
		6		6-7-0-1-2-3-4-5	6-7-8-9-10-11-12-13-14-15-0-1-2-3-4-5	6-7-8-9-10-11-12-...
		7		7-0-1-2-3-4-5-6	7-8-9-10-11-12-13-14-15-0-1-2-3-4-5-6	7-8-9-10-11-12-13-…
		…			…	…
		14			14-15-0-1-2-3-4-5-6-7-8-9-10-11-12-13	14-15-16-17-18-19-20-…
		15			15-0-1-2-3-4-5-6-7-8-9-10-11-12-13-14	15-16-17-18-19-20-21-…
1	No	0	0-1-2-3	0-1-2-3-4-5-6-7	0-1-2-3-4-5-6-7-8-9-10-11-12-13-14-15	0-1-2-3-4-5-6-…
		1	1-2-3-4	1-2-3-4-5-6-7-8	1-2-3-4-5-6-7-8-9-10-11-12-13-14-15-16	1-2-3-4-5-6-7-…
		2	2-3-4-5	2-3-4-5-6-7-8-9	2-3-4-5-6-7-8-9-10-11-12-13-14-15-16-17	2-3-4-5-6-7-8-…
		3	3-4-5-6	3-4-5-6-7-8-9-10	3-4-5-6-7-8-9-10-11-12-13-14-15-16-17-18	3-4-5-6-7-8-9-…
		4		4-5-6-7-8-9-10-11	4-5-6-7-8-9-10-11-12-13-14-15-16-17-18-19	4-5-6-7-8-9-10-…
		5		5-6-7-8-9-10-11-12	5-6-7-8-9-10-11-12-13-14-15-16-17-18-19-20	5-6-7-8-9-10-11-…
		6		6-7-8-9-10-11-12-13	6-7-8-9-10-11-12-13-14-15-16-17-18-19-20-21	6-7-8-9-10-11-12-…
		7		7-8-9-10-11-12-13-14	7-8-9-10-11-12-13-14-...-17-18-19-20-21-22	7-8-9-10-11-12-13-…
		…			…	…
		14			14-15-16-17-18-19-...-23-24-25-26-27-28-29	14-15-16-17-18-19-20-…
		15			15-16-17-18-19-20-...-24-25-26-27-28-29-30	15-16-17-18-19-20-21-…

Burst Length (BCR[2:0]) Default = Continuous Burst

Burst lengths define the number of words the device outputs during a burst READ operation. The device supports a burst length of 4, 8, or 16 words. The device can also be set in continuous burst mode where data is output sequentially without regard to address boundaries; the internal address wraps to 00000h if the device is read past the last address. WRITE bursts are always performed using continuous burst mode.

Burst Wrap (BCR[3]) Default = Burst No Wrap (Within Burst Length)

The burst wrap option determines whether a 4-, 8-, or 16-word burst READ wraps within the burst length or steps through sequential addresses. If the wrap option is not enabled, the device outputs data from sequential addresses without regard to burst boundaries; the internal address wraps to 00000h if the device is read past the last address.

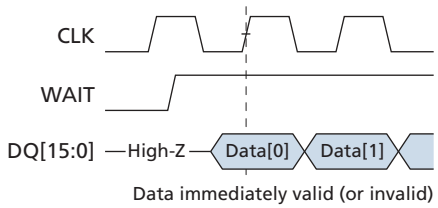
Output Impedance (BCR[5]) Default = Outputs Use Full-Drive Strength

The output driver strength can be altered to adjust for different data bus loading scenarios. The reduced-strength option should be more than adequate in stacked chip (Flash + CellularRAM) environments when there is a dedicated memory bus. The reduced-drive-strength option is included to minimize noise generated on the data bus during READ operations. Normal output impedance should be selected when using a discrete CellularRAM device in a more heavily loaded data bus environment. Partial drive is approximately one-quarter-full drive strength. Outputs are configured at full-drive strength during testing.

WAIT Configuration (BCR[8]) Default = WAIT Transitions One Clock Before Data Valid/Invalid

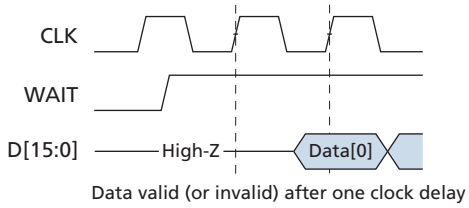
The WAIT configuration bit is used to determine when WAIT transitions between the asserted and the deasserted state with respect to valid data presented on the data bus. The memory controller will use the WAIT signal to coordinate data transfer during synchronous READ and WRITE operations. When BCR[8] = 0, data will be valid or invalid on the clock edge immediately after WAIT transitions to the deasserted or asserted state, respectively (see Figure 20 and Figure 22 on page 27). When BCR[8] = 1, the WAIT signal transitions one clock period prior to the data bus going valid or invalid (see Figures 21 and Figure 22 on page 27).

Figure 20: WAIT Configuration (BCR[8] = 0)



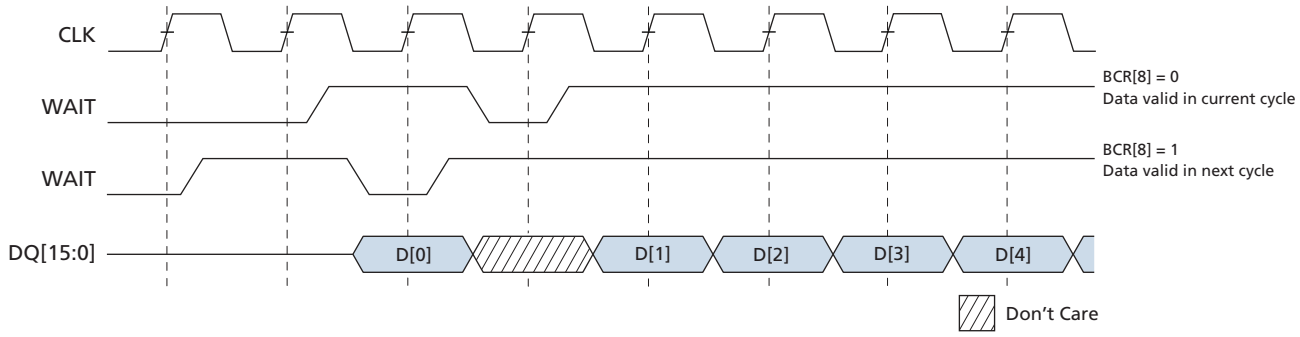
Note: Data valid/invalid immediately after WAIT transitions (BCR[8] = 0). See Figure 22 on page 27.

Figure 21: WAIT Configuration (BCR[8] = 1)



Note: Valid/invalid data delayed for one clock after WAIT transitions (BCR[8] = 1). See Figure 22 on page 27.

Figure 22: WAIT Configuration During Burst Operation



Note: Nondefault BCR setting for WAIT during BURST operation: WAIT active LOW.

WAIT Polarity (BCR[10]) Default = WAIT Active HIGH

The WAIT polarity bit indicates whether an asserted WAIT output should be HIGH or LOW. This bit will determine whether the WAIT signal requires a pull-up or pull-down resistor to maintain the deasserted state.

Latency Counter (BCR[13:11]) Default = Three-Clock Latency

The latency counter bits determine how many clocks occur between the beginning of a READ or WRITE operation and the first data value transferred. Only latency code 2 (3 clocks) or latency code 3 (4 clocks) is allowed (see Table 5 and Figure 23).

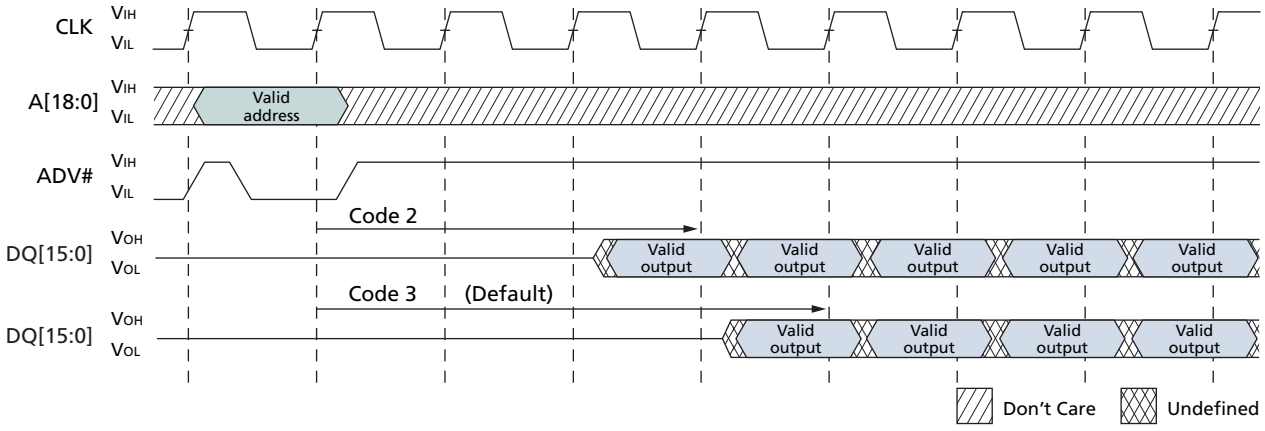
Operating Mode (BCR[15]) Default = Asynchronous Operation

The operating mode bit either selects synchronous BURST operation or the default asynchronous mode of operation.

Table 5: Latency Configuration

Latency Configuration Code	Max Input CLK Frequency	
	104 MHz	80 MHz
2 (3 clocks)	66 (15ns)	53 (18.75ns)
3 (4 clocks) – default	104 (9.62ns)	80 (12.5ns)

Figure 23: Latency Counter (Variable Latency, No Refresh Collision)



Refresh Configuration Register

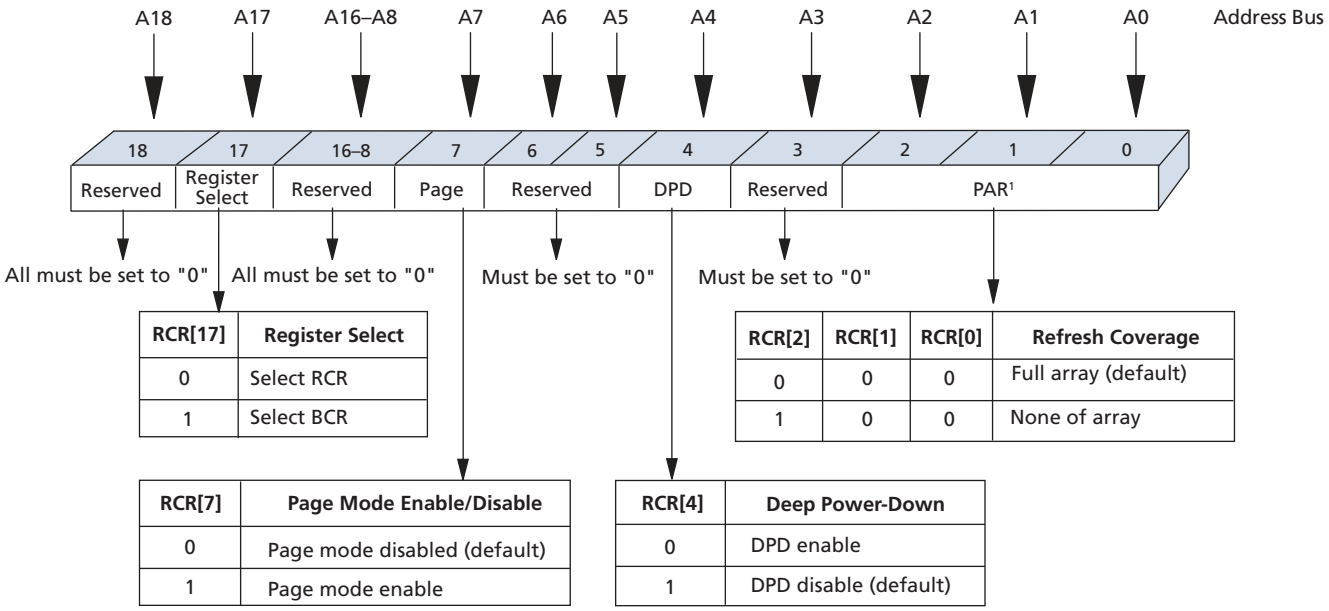
The refresh configuration register (RCR) defines how the CellularRAM device performs its transparent self refresh. Altering the refresh parameters can dramatically reduce current consumption during standby mode. Page mode control is also embedded into the RCR. Figure 24 describes the control bits used in the RCR. At power-up, the RCR is set to 0010h.

The RCR is accessed using CRE and A[17] LOW or through the configuration register software-access sequence with DQ = 0000h on the third cycle (see "Configuration Registers" on page 18).

Partial-Array Refresh (RCR[2:0]) Default = Full Array Refresh

The PAR bits restrict refresh operation to a portion of the total memory array. The refresh options are full array or none of the array.

Figure 24: Refresh Configuration Register Mapping



Notes: 1. Other settings result in full-array refresh coverage.

Deep Power-Down (RCR[4]) Default = DPD Disabled

The deep power-down bit enables and disables all refresh-related activity. This mode is used if the system does not require the storage provided by the CellularRAM device. Any stored data will become corrupted when DPD is enabled. When refresh activity has been reenabled, the CellularRAM device will require 150µs to perform an initialization procedure before normal operations can resume.

Deep power-down is enabled when RCR[4] = 0 and remains enabled until RCR[4] is set to "1." DPD should not be enabled or disabled with the software-access sequence; instead, use CRE to access the RCR.

Page Mode Operation (RCR[7]) Default = Disabled

The page mode operation bit determines whether page mode is enabled for asynchronous READ operations. In the power-up default state, page mode is disabled.

Electrical Characteristics

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Table 6: Absolute Maximum Ratings

Parameter	Rating
Voltage to any ball except V_{CC}; V_{CCQ} relative to V_{SS}	–0.5V to (4.0V or V_{CCQ} + 0.3V, whichever is less)
Voltage on V_{CC} supply relative to V_{SS}	–0.2V to +2.45V
Voltage on V_{CCQ} supply relative to V_{SS}	–0.2V to +4.0V
Storage temperature (plastic)	–55ºC to +150ºC
Operating temperature (case) Wireless[1] Industrial	 –30ºC to +85ºC –40ºC to +85ºC
Soldering temperature and time 10 seconds (solder ball only)	 +260ºC

Notes: 1. –30°C exceeds the CellularRAM Workgroup 1.0 specification of –25°C.

Table 7: Electrical Characteristics and Operating Conditions

Wireless temperature[1] (–30ºC < T_C < +85ºC); Industrial temperature (–40ºC < T_C < +85ºC)

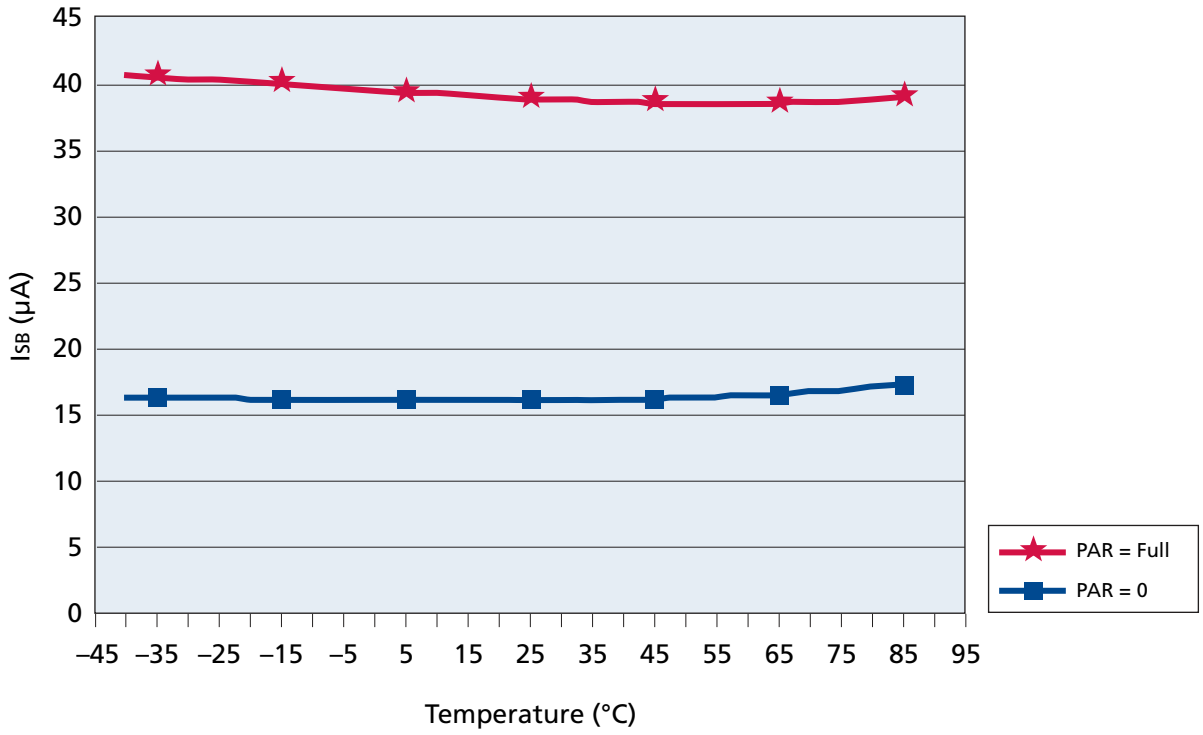
Description	Conditions	Symbol		Min	Max	Unit	Notes
Supply voltage		V_{CC}		1.7	1.95	V	
I/O supply voltage		V_{CCQ}		1.7	3.6	V	
Input high voltage		V_{IH}		V_{CCQ} - 0.4	V_{CCQ} + 0.2	V	2, 3
Input low voltage		V_{IL}		–0.2	0.4	V	4
Output high voltage	I_{OH} = –0.2mA	V_{OH}		0.8 V_{CCQ}	–	V	5
Output low voltage	I_{OL} = +0.2mA	V_{OL}		–	0.2 V_{CCQ}	V	5
Input leakage current	V_{IN} = 0 to V_{CCQ}	I_{LI}		–	1	µA	
Output leakage current	OE# = V_{IH} or chip disabled	I_{LO}		–	1	µA	
Operating Current		**Symbol**		**TYP**	**Max**	**Unit**	**Notes**
Asynchronous random READ/WRITE	V_{IN} = V_{CCQ} or 0V chip enabled, I_{OUT} = 0	I_{CC1}	–70	–	20	mA	6
					–		
Asynchronous page READ		I_{CC1P}	–70	–	15	mA	6
					–		
Initial access, burst READ/WRITE		I_{CC2}	104 MHz	–	35	mA	6
			80 MHz		30		
Continuous burst READ		I_{CC3R}	104 MHz	–	28	mA	6
			80 MHz		22		
Continuous burst WRITE		I_{CC3W}	104 MHz	–	33	mA	6
			80 MHz		25		
Standby current	V_{IN} = V_{CCQ} or 0V CE# = V_{CCQ}	I_{SB}	Standard	–	65	µA	7

Notes:
1. The 3.6V I/O and the –30°C wireless temperature exceed the CellularRAM Workgroup 1.0 specification of –25°C.
2. Input signals may overshoot to V_{CCQ} + 1.0V for periods less than 2ns during transitions.
3. V_{IH} (MIN) value is not aligned with CellularRAM Workgroup 1.0 specification of V_{CCQ} - 0.4V.
4. Input signals may undershoot to V_{SS} - 1.0V for periods less than 2ns during transitions.
5. BCR[5] = 0b.
6. This parameter is specified with the outputs disabled to avoid external loading effects. The user must add the current required to drive output capacitance expected in the actual system.
7. I_{SB} (MAX) values measured with PAR set to FULL ARRAY. To achieve low standby current, all inputs must be driven either to V_{CCQ} or V_{SS}. I_{SB} might be slightly higher for up to 500ms after power-up, after changes to the PAR array partition, or when entering standby mode.

Typical Standby Currents

The following figure refers to typical standby currents for the device.

Figure 25: Typical Refresh Current vs. Temperature



Note: Typical I_{SB} currents for each PAR setting.

Table 8: Deep Power-Down Specifications

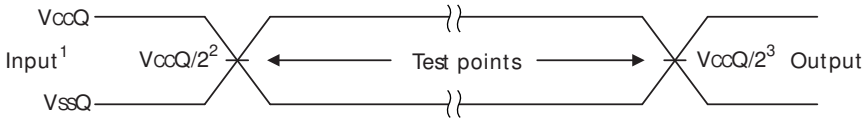
Description	Conditions	Symbol	Typ	Unit
Deep power-down	V_{IN} = V_{CCQ} or 0V; +25°C	I_{ZZ}	10	µA

Table 9: Capacitance

Description	Conditions	Symbol	Min	Max	Unit	Notes
Input capacitance	T_C = +25ºC; f = 1 MHz; V_{IN} = 0V	C_{IN}	2.0	6.5	pF	1
Input/output capacitance (DQ)		C_{IO}	3.0	6.5	pF	1

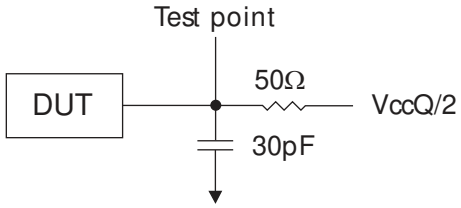
Notes: 1. These parameters are verified in device characterization and are not 100% tested.

Figure 26: AC Input/Output Reference Waveform



Notes: 1. AC test inputs are driven at V_{CCQ} for a logic 1 and V_{SSQ} for a logic 0. Input rise and fall times (10% to 90%) <1.6ns.
2. Input timing begins at V_{CCQ}/2.
3. Output timing ends at V_{CCQ}/2.

Figure 27: Output Load Circuit



Notes: 1. All tests are performed with the outputs configured for full-drive strength (BCR[5] = 0b).

Timing Requirements

Table 10: Asynchronous READ Cycle Timing Requirements

Parameter[1]	Symbol	70ns		Unit	Notes
		Min	Max		
Address access time	tAA	–	70	ns	
ADV# access time	tAADV	–	70	ns	
Page access time	tAPA	–	20	ns	
Address hold from ADV# HIGH	tAVH	5	–	ns	
Address setup to ADV# HIGH	tAVS	5	–	ns	
LB#/UB# access time	tBA	–	70	ns	
LB#/UB# disable to DQ High-Z output	tBHZ	–	8	ns	2
LB#/UB# enable to Low-Z output	tBLZ	10	–	ns	3
Maximum CE# pulse width	tCEM	–	8	µs	4
CE# LOW to WAIT valid	tCEW	1	7.5	ns	
Chip select access time	tCO	–	70	ns	
CE# LOW to ADV# HIGH	tCVS	10	–	ns	
Chip disable to DQ and WAIT High-Z output	tHZ	–	8	ns	2
Chip enable to Low-Z output	tLZ	10	–	ns	3
Output enable to valid output	tOE	–	20	ns	
Output hold from address change	tOH	5	–	ns	
Output disable to DQ High-Z output	tOHZ	–	8	ns	2
Output enable to Low-Z output	tOLZ	3	–	ns	3
Page cycle time	tPC	20	–	ns	
READ cycle time	tRC	70	–	ns	
ADV# pulse width LOW	tVP	10	–	ns	
ADV# pulse width HIGH	tVPH	10	–	ns	

Notes:
1. All tests are performed with the outputs configured for full-drive strength (BCR[5] = 0b).
2. Low-Z to High-Z timings are tested with the circuit shown in Figure 27 on page 32. The High-Z timings measure a 100mV transition either from V_{OH} or V_{OL} toward $V_{CCQ}/2$.
3. High-Z to Low-Z timings are tested with the circuit shown in Figure 27 on page 32. The Low-Z timings measure a 100mV transition away from the High-Z ($V_{CCQ}/2$) level either toward V_{OH} or V_{OL}.
4. Page mode enabled only.

Table 11: Burst READ Cycle Timing Requirements

Parameter[1]	Symbol	104 MHz		80 MHz		Unit	Notes
		Min	Max	Min	Max		
Burst to READ access time	^{t}ABA	–	35.9	–	46.5	ns	
CLK to output delay	^{t}ACLK	–	7	–	9	ns	
Burst OE# LOW to output delay	^{t}BOE	–	20	–	20	ns	
CE# HIGH between subsequent burst and mixed-mode operations	^{t}CBPH	5	–	5	–	ns	2
Maximum CE# pulse width	^{t}CEM	–	8	–	8	µs	
CE# LOW to WAIT valid	^{t}CEW	1	7.5	1	7.5	ns	
CLK period	^{t}CLK	9.62	–	12.5	–	ns	
CE# setup time to active CLK edge	^{t}CSP	3	–	4.5	–	ns	
Hold time from active CLK edge	^{t}HD	2	–	2	–	ns	
Chip disable to DQ and WAIT High-Z output	^{t}HZ	–	8	–	8	ns	3
CLK rise or fall time	^{t}KHKL	–	1.6	–	1.8	ns	
CLK to WAIT valid	^{t}KHTL	–	7	–	9	ns	
Output HOLD from CLK	^{t}KOH	2	–	2	–	ns	
CLK HIGH or LOW time	^{t}KP	3	–	4	–	ns	
Output disable to DQ High-Z output	^{t}OHZ	–	8	–	8	ns	3
Output enable to Low-Z output	^{t}OLZ	3	–	3	–	ns	4
Setup time to active CLK edge	^{t}SP	3	–	3	–	ns	

Notes:
1. All tests are performed with the outputs configured for full-drive strength (BCR[5] = 0b).
2. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns.
3. Low-Z to High-Z timings are tested with the circuit shown in Figure 27 on page 32. The High-Z timings measure a 100mV transition either from V_{OH} or V_{OL} toward $V_{CCQ}/2$.
4. High-Z to Low-Z timings are tested with the circuit shown in Figure 27 on page 32. The Low-Z timings measure a 100mV transition away from the High-Z ($V_{CCQ}/2$) level either toward V_{OH} or V_{OL}.

Table 12: Asynchronous WRITE Cycle Timing Requirements

Parameter	Symbol	70ns		Unit	Notes
		Min	Max		
Address and ADV# LOW setup time	tAS	0	–	ns	
Address hold from ADV# going HIGH	tAVH	5	–	ns	
Address setup to ADV# going HIGH	tAVS	5	–	ns	
Address valid to end of WRITE	tAW	70	–	ns	
LB#/UB# select to end of WRITE	tBW	70	–	ns	
CE# LOW to WAIT valid	tCEW	1	7.5	ns	
Asynchronous address-to-burst transition time	tCKA	70	–	ns	
CE# HIGH between subsequent asynchronous operations	tCPH	5	–	ns	
CE# LOW to ADV# HIGH	tCVS	10	–	ns	
Chip enable to end of WRITE	tCW	70	–	ns	
Data hold from WRITE time	tDH	0	–	ns	
Data WRITE setup time	tDW	23	–	ns	
Chip disable to WAIT High-Z output	tHZ	–	8	ns	
Chip enable to Low-Z output	tLZ	10	–	ns	2
End WRITE to Low-Z output	tOW	5	–	ns	1
ADV# pulse width	tVP	10	–	ns	
ADV# pulse width HIGH	tVPH	10	–	ns	
ADV# setup to end of WRITE	tVS	70	–	ns	
WRITE cycle time	tWC	70	–	ns	
WRITE to DQ High-Z output	tWHZ	–	8	ns	2
WRITE pulse width	tWP	46	–	ns	3
WRITE pulse width HIGH	tWPH	10	–	ns	
WRITE recovery time	tWR	0	–	ns	

Notes:
1. High-Z to Low-Z timings are tested with the circuit shown in Figure 27 on page 32. The Low-Z timings measure a 100mV transition away from the High-Z ($V_{CCQ}/2$) level either toward V_{OH} or V_{OL}.
2. Low-Z to High-Z timings are tested with the circuit shown in Figure 27 on page 32. The High-Z timings measure a 100mV transition either from V_{OH} or V_{OL} toward $V_{CCQ}/2$.
3. WE# LOW time must be limited to tCEM (8µs).

Table 13: Burst WRITE Cycle Timing Requirements

Parameter	Symbol	104 MHz		80 MHz		Unit	Notes
		Min	Max	Min	Max		
CE# HIGH between subsequent burst and mixed-mode operations	^{t}CBPH	5	–	5	–	ns	1
Minimum CE# pulse width	^{t}CEM	–	8	–	8	µs	1
CE# LOW to WAIT valid	^{t}CEW	1	7.5	1	7.5	ns	
Clock period	^{t}CLK	9.62	–	12.5	–	ns	
CE# setup to CLK active edge	^{t}CSP	3	–	4.5	–	ns	
Hold time from active CLK edge	^{t}HD	2	–	2	–	ns	
Chip disable to WAIT High-Z output	^{t}HZ	–	8	–	8	ns	
CLK rise or fall time	^{t}KHKL	–	1.6	–	1.8	ns	
Clock to WAIT valid	^{t}KHTL	–	7	–	9	ns	
CLK HIGH or LOW time	^{t}KP	3	–	4	–	ns	
Setup time to active CLK edge	^{t}SP	3	–	3	–	ns	

Notes: 1. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns.

Figure 28: Initialization Period

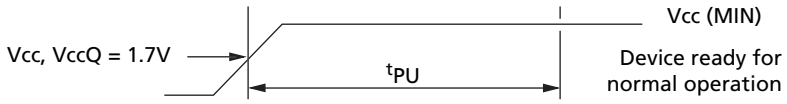


Table 14: Initialization Timing Parameters

Parameter	Symbol	-70		Unit
		Min	Max	
Initialization period (required before normal operations)	^{t}PU	–	150	µs

Timing Diagrams

Figure 29: Asynchronous READ

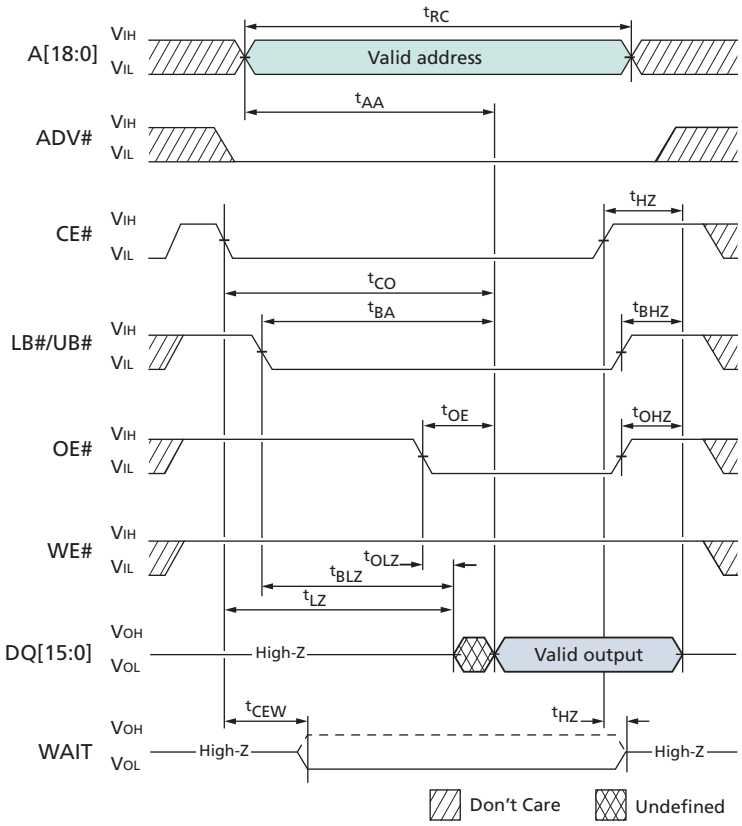


Figure 30: Asynchronous READ Using ADV#

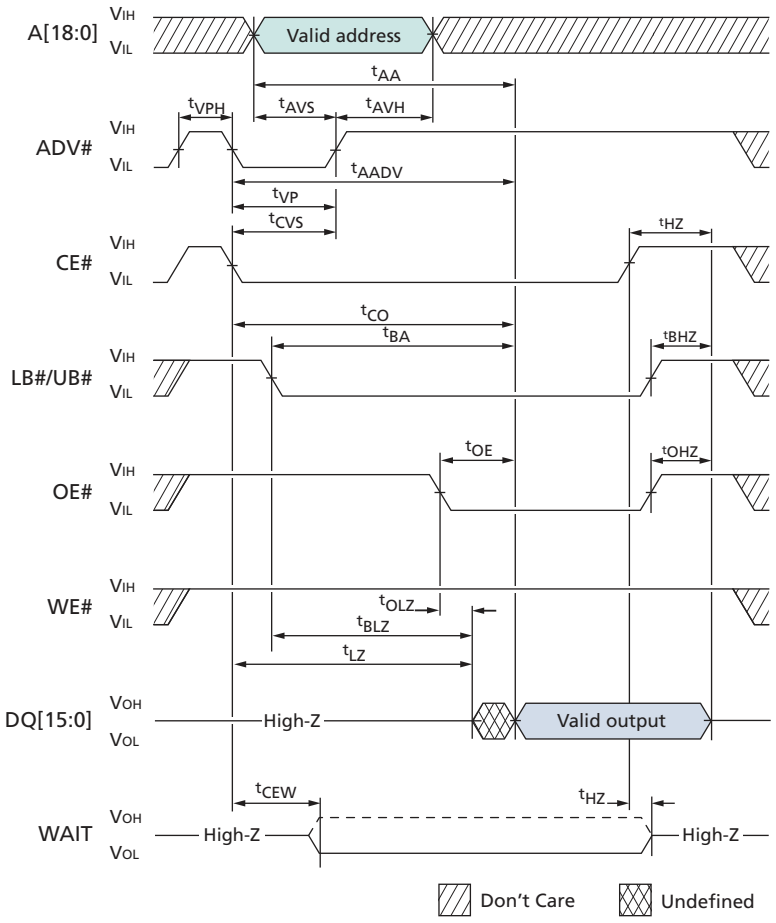


Figure 31: Page Mode READ

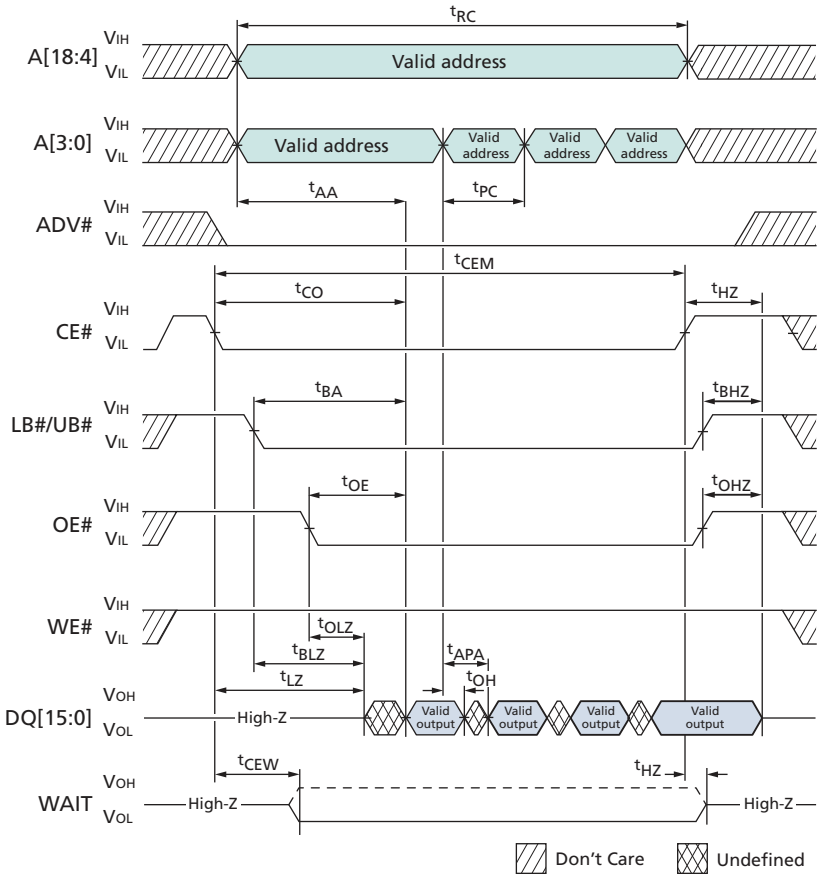
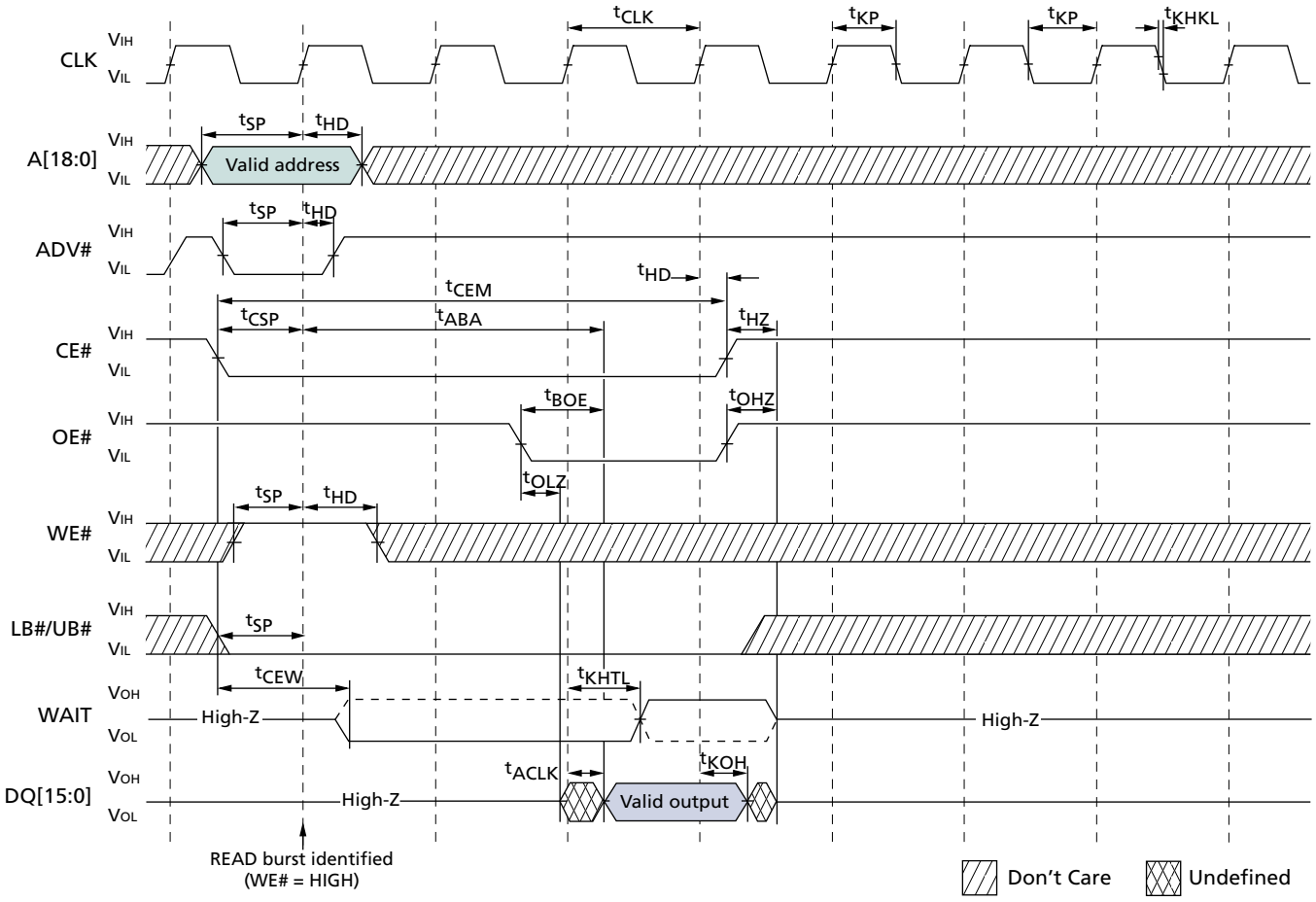
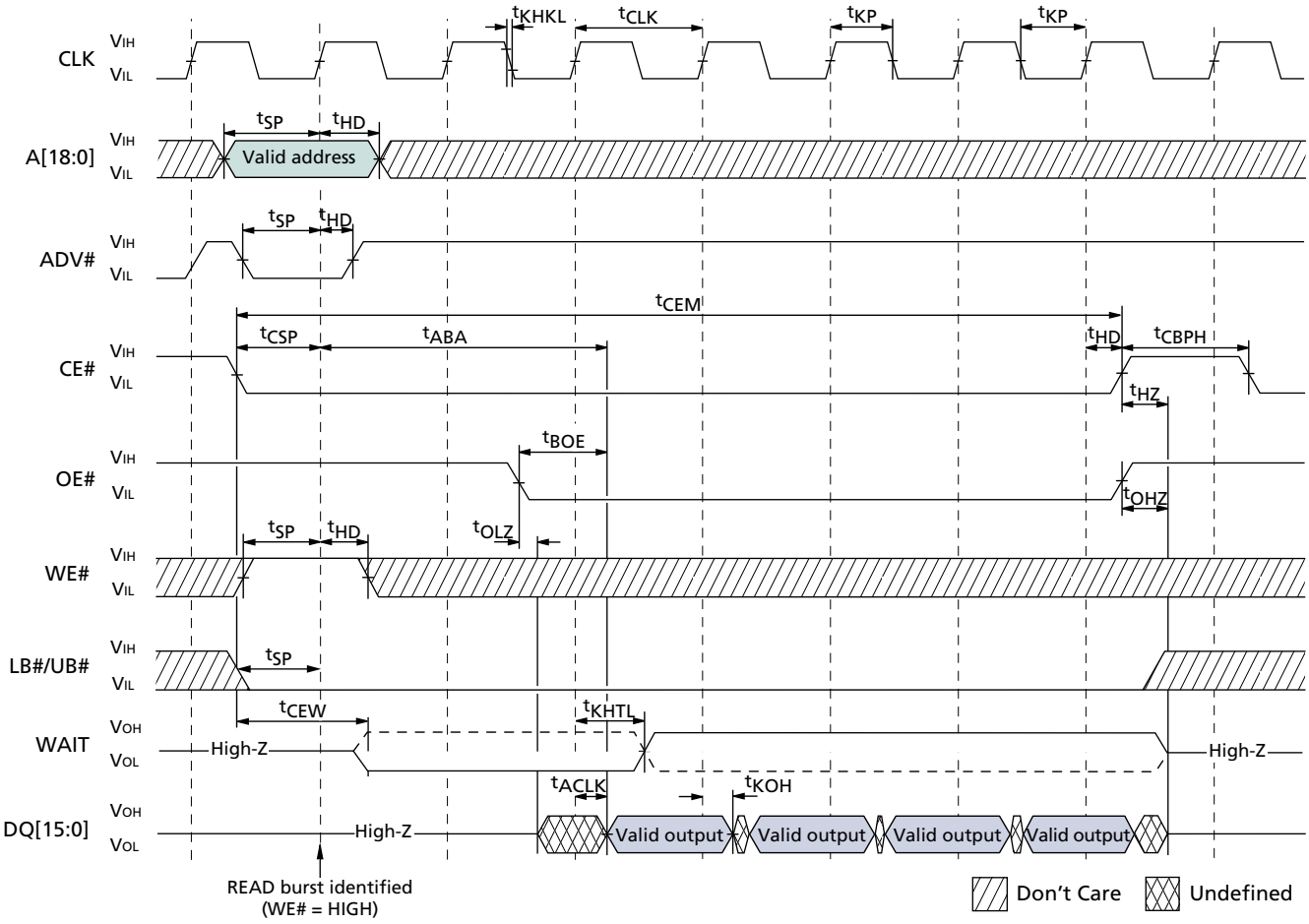


Figure 32: Single-Access Burst READ Operation



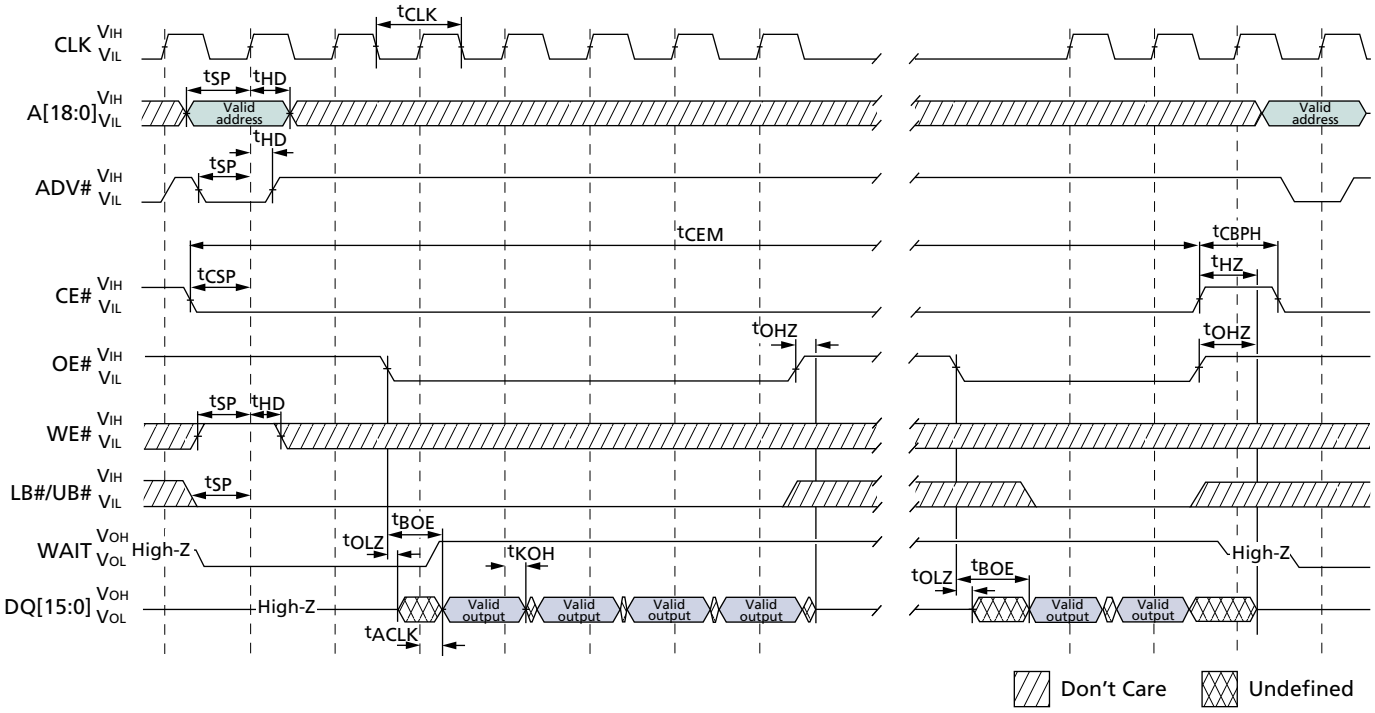
Notes: 1. Nondefault BCR settings for single-access burst READ operation: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Figure 33: Four-Word Burst READ Operation



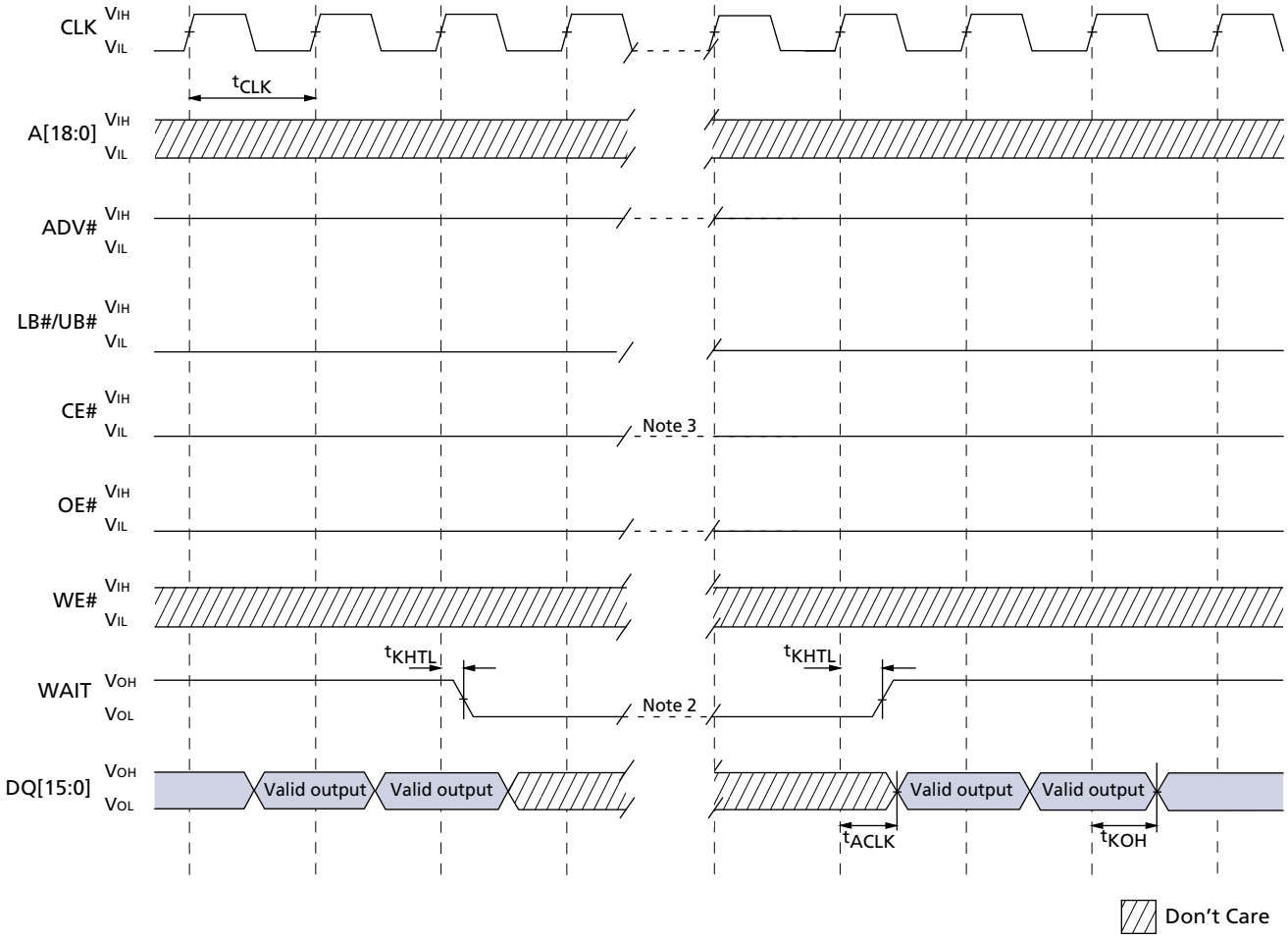
Notes: 1. Nondefault BCR settings for 4-word burst READ operation: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Figure 34: READ Burst Suspend



Notes: 1. Nondefault BCR settings for READ burst suspend: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.

Figure 35: Output Delay in Continuous Burst READ with BCR[8] = 0 for End-of-Row Condition



Notes:
1. Nondefault BCR settings for continuous burst READ showing an output delay, BCR[8] = 0 for end-of-row condition: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. WAIT will be asserted a maximum of (LC) cycles (BCR[8] = 0; WAIT asserted during delay). LC = latency code (BCR[13:11]).
3. CE# must not remain LOW longer than ^{t}CEM.

Figure 36: CE#-Controlled Asynchronous WRITE

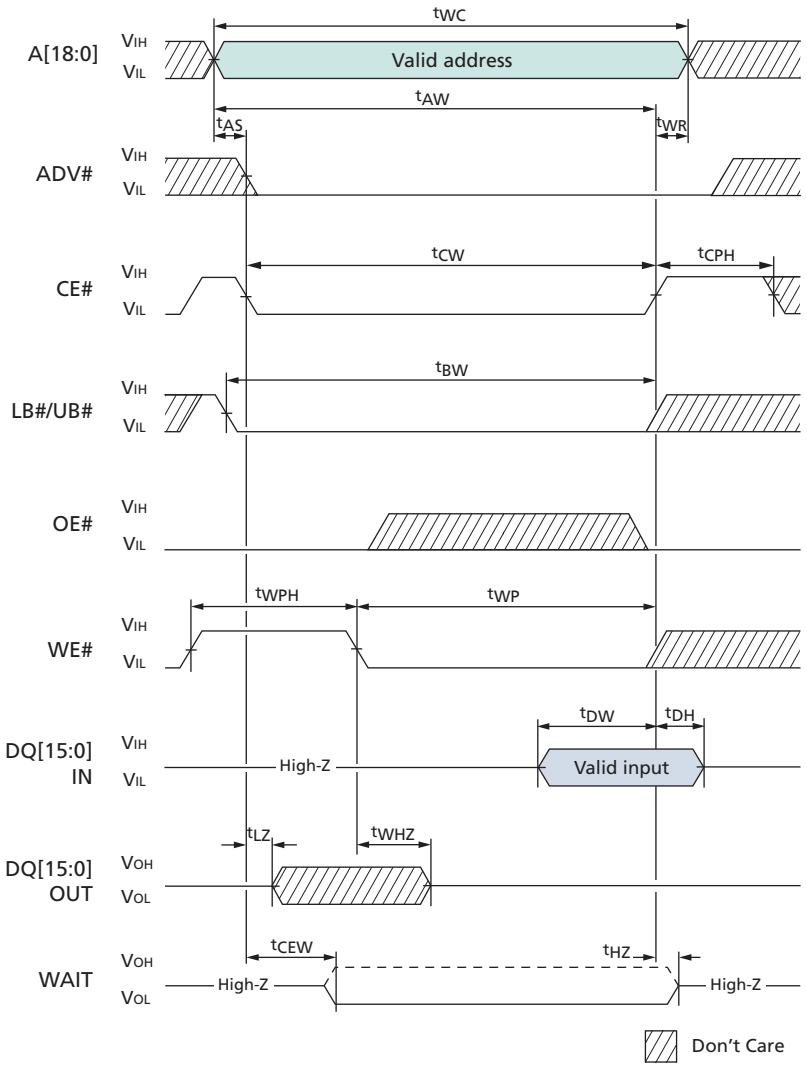


Figure 37: LB#/UB#-Controlled Asynchronous WRITE

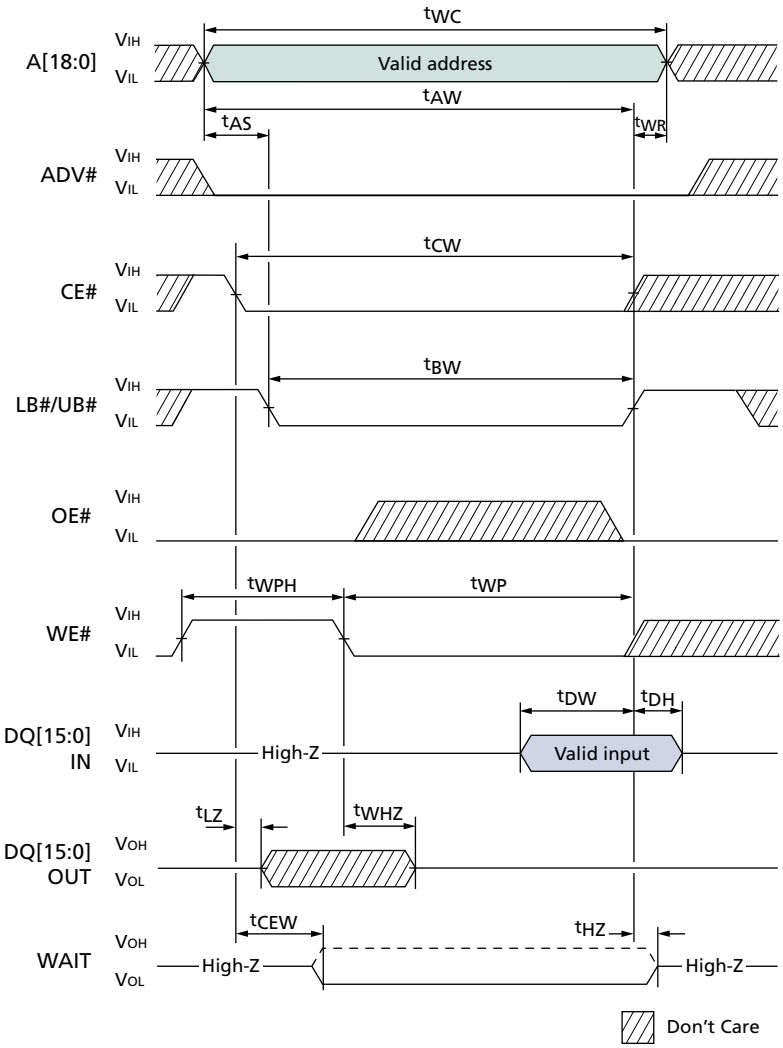


Figure 38: WE#-Controlled Asynchronous WRITE

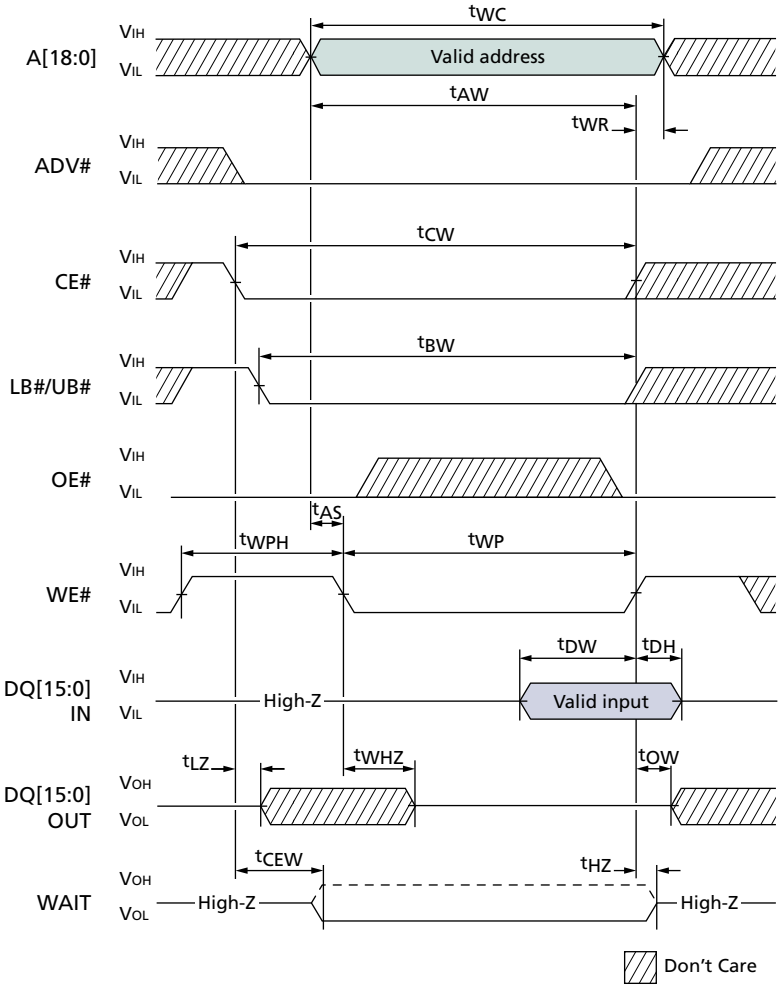


Figure 39: Asynchronous WRITE Using ADV#

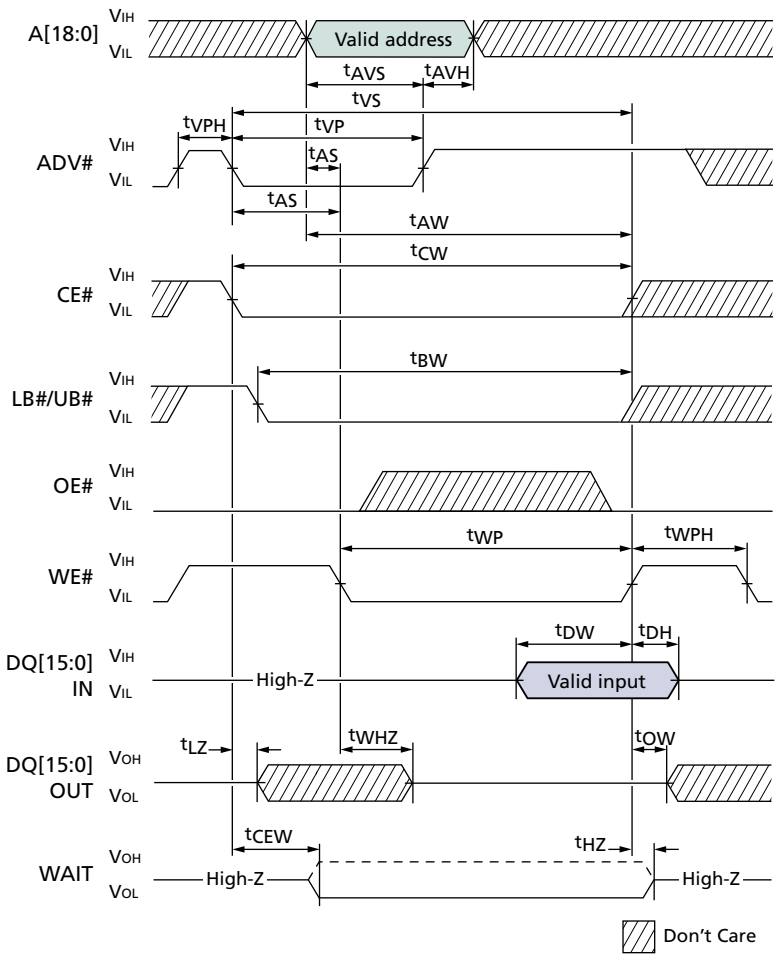
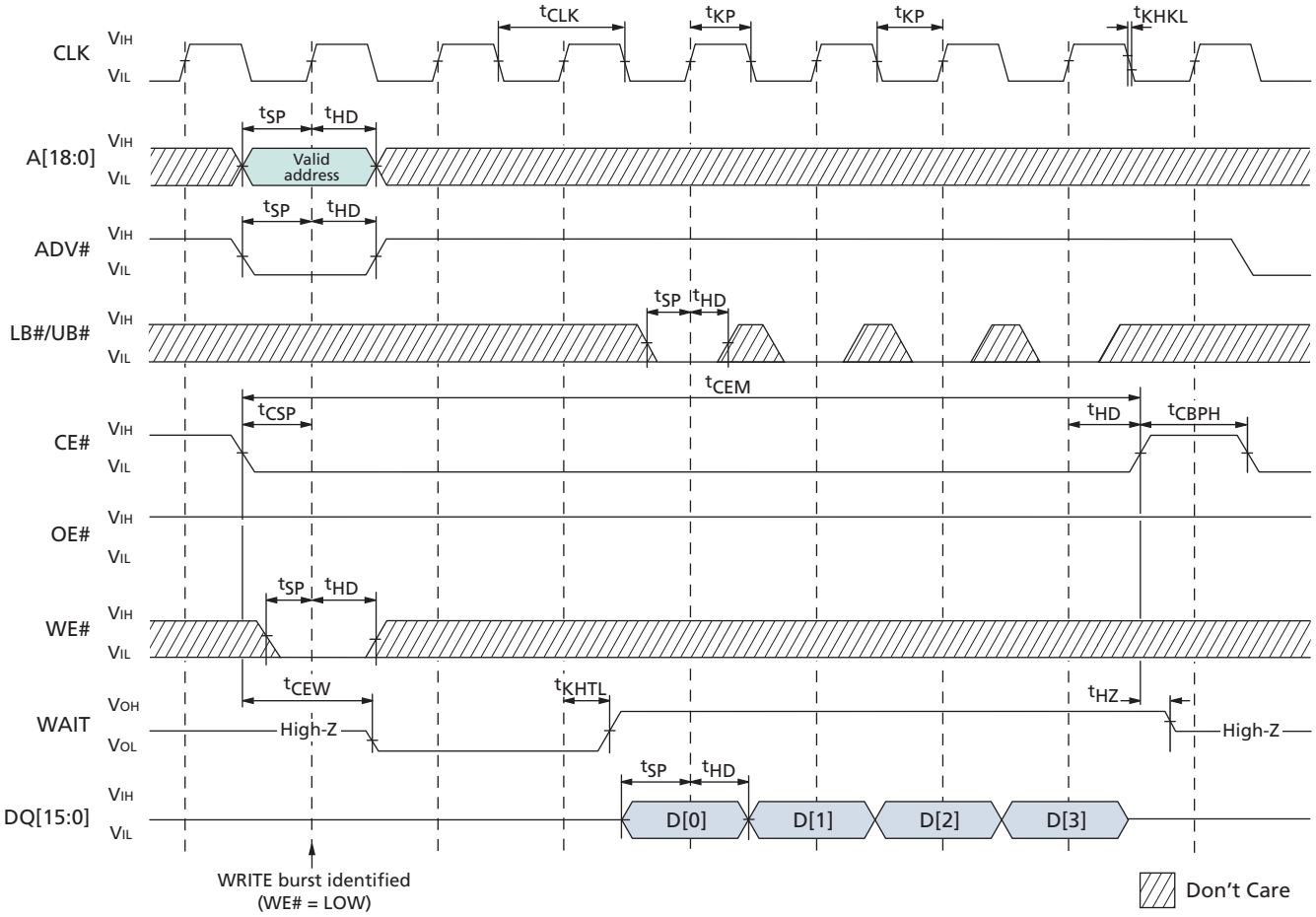
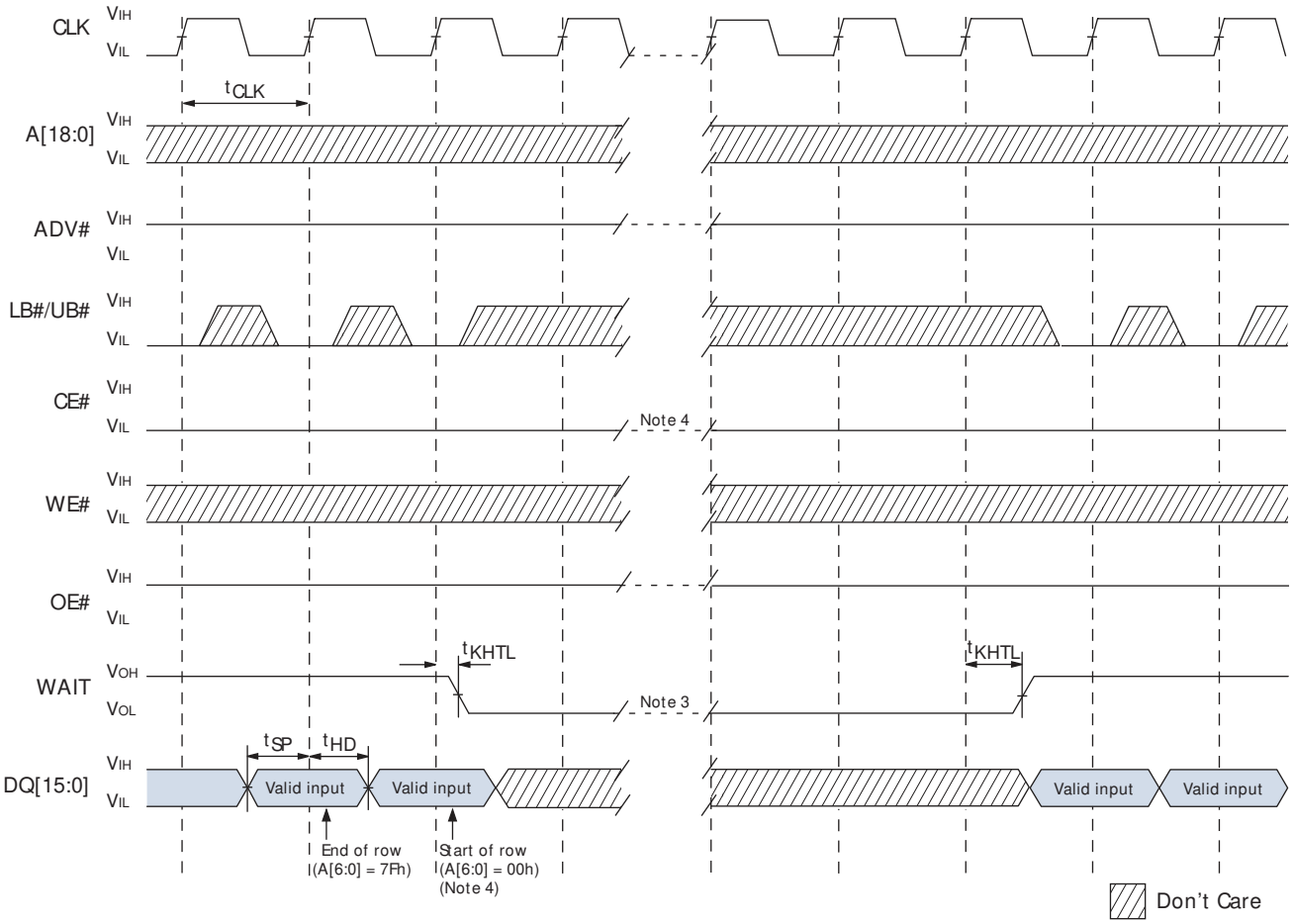


Figure 40: Burst WRITE Operation



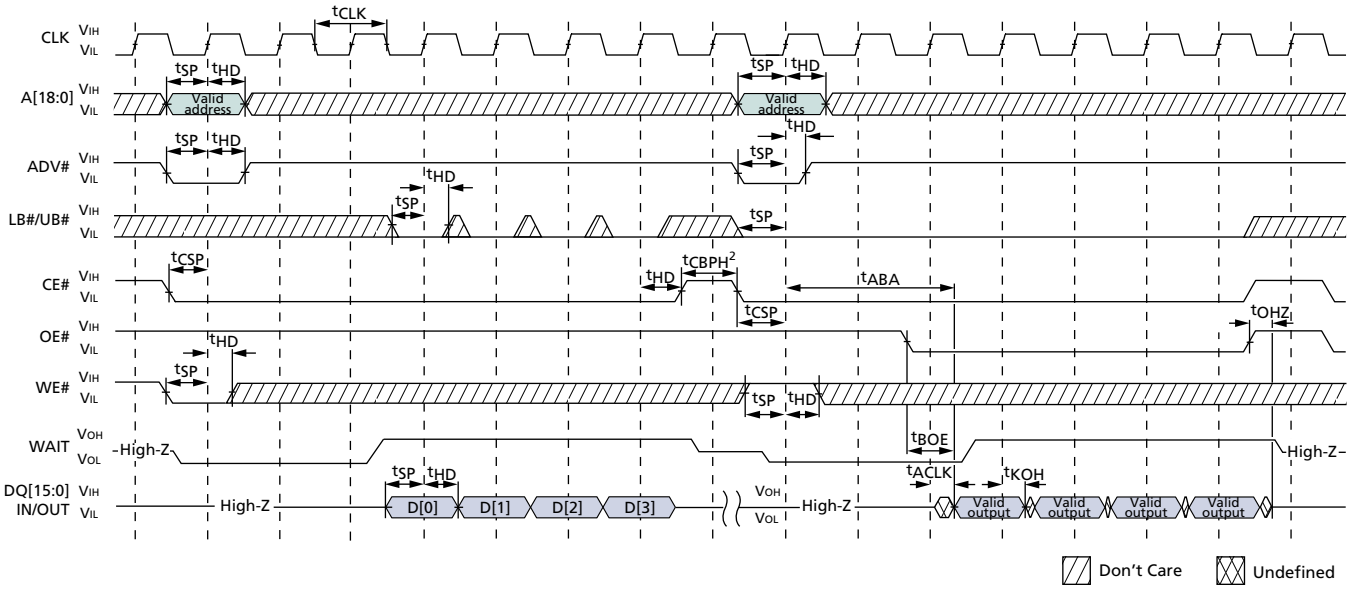
Notes: 1. Nondefault BCR settings for burst WRITE operation: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted.

Figure 41: Output Delay in Continuous Burst Write with BCR[8] = 0 for End-of-Row Condition



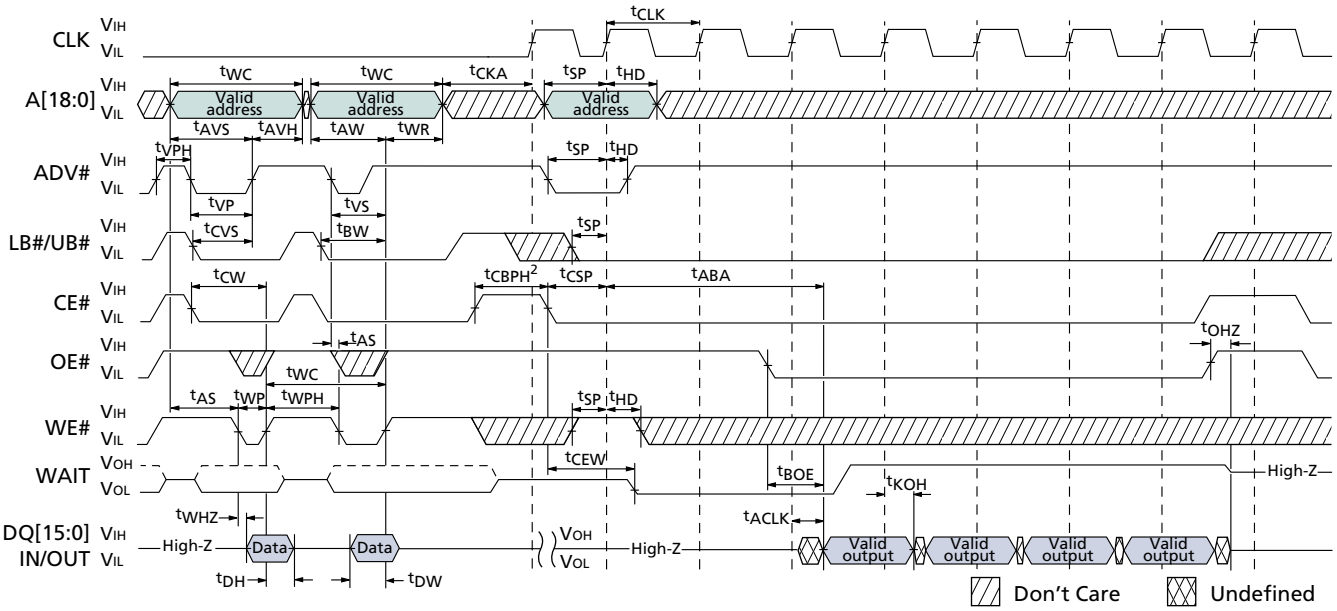
Notes:
1. Nondefault BCR settings for continuous burst WRITE, BCR[8] = 0; WAIT active LOW; WAIT asserted during delay. Do not cross row boundaries with fixed latency.
2. CE# must not remain LOW longer than ^{t}CEM.
3. WAIT asserts anywhere from LC to 2LC cycles. LC = latency code (BCR[13:11]).
4. Taking CE# HIGH or ADV# LOW on the start-of-row cycle will abort the burst and not write the start-of-row data. Devices from different CellularRAM vendors can assert WAIT so that the start-of-row data is input just before (as shown) or just after WAIT asserts. This difference in behavior will not be noticed by controllers that monitor WAIT or that use WAIT to abort on the start-of-row input cycle.

Figure 42: Burst WRITE Followed by Burst READ



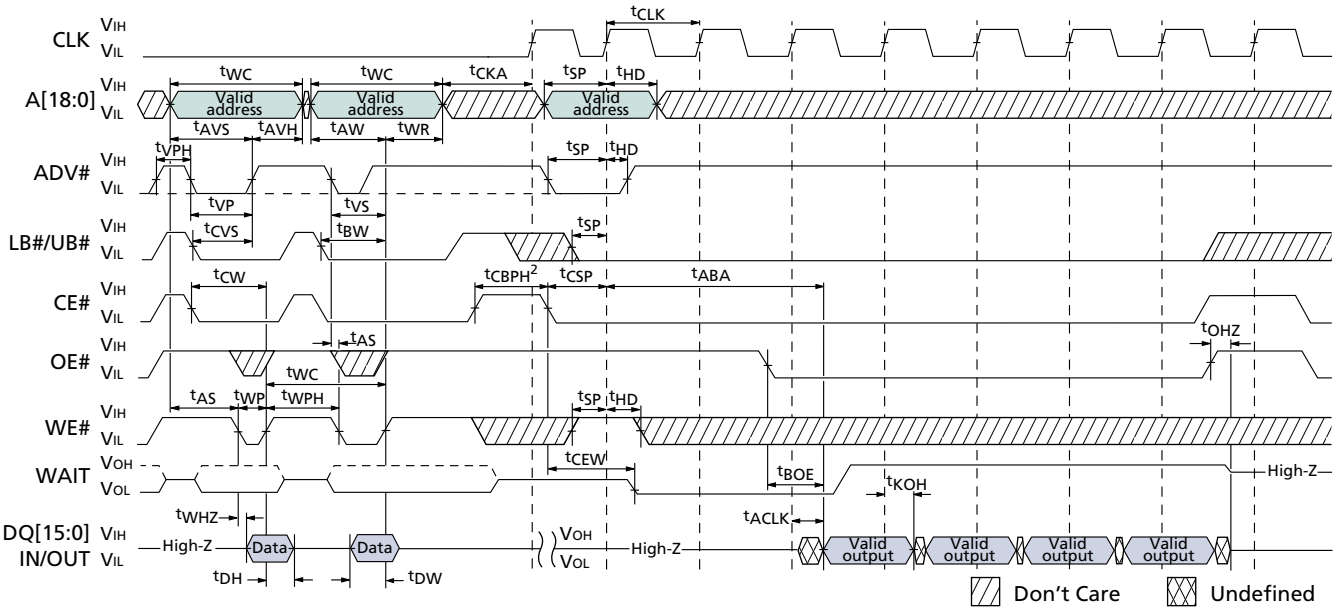
Notes:
1. Nondefault BCR settings for burst WRITE followed by burst READ: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns. Note that the CellularRAM Workgroup 1.0 specification requires CE# to be clocked HIGH to terminate the burst.

Figure 43: Asynchronous WRITE Followed by Burst READ



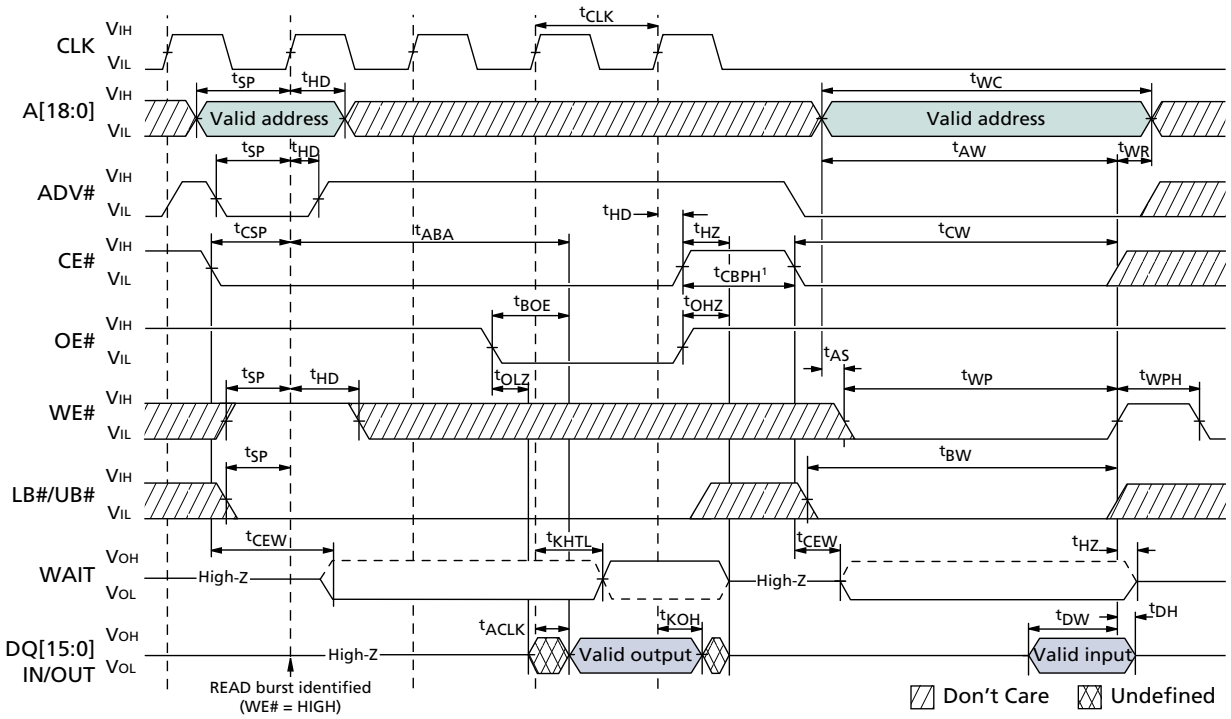
Notes:
1. Nondefault BCR settings for asynchronous WRITE followed by burst READ: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns. Note that the CellularRAM Workgroup 1.0 specification requires CE# to be clocked HIGH to terminate the burst.

Figure 44: Asynchronous WRITE Followed by Burst READ with ADV# LOW



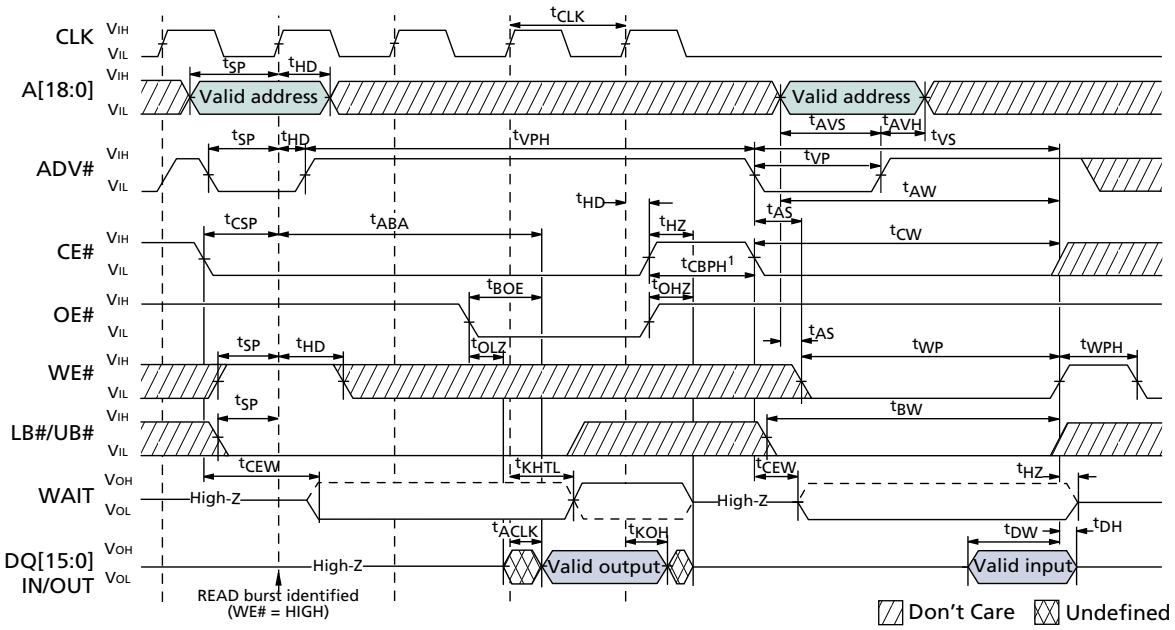
Notes:
1. Nondefault BCR settings for asynchronous WRITE followed by burst READ: latency code 2 (3 clocks); WAIT active LOW; WAIT asserted during delay.
2. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns. Note that the CellularRAM Workgroup 1.0 specification requires CE# to be clocked HIGH to terminate the burst.

Figure 45: Burst READ Followed by Asynchronous WRITE (WE#-Controlled)



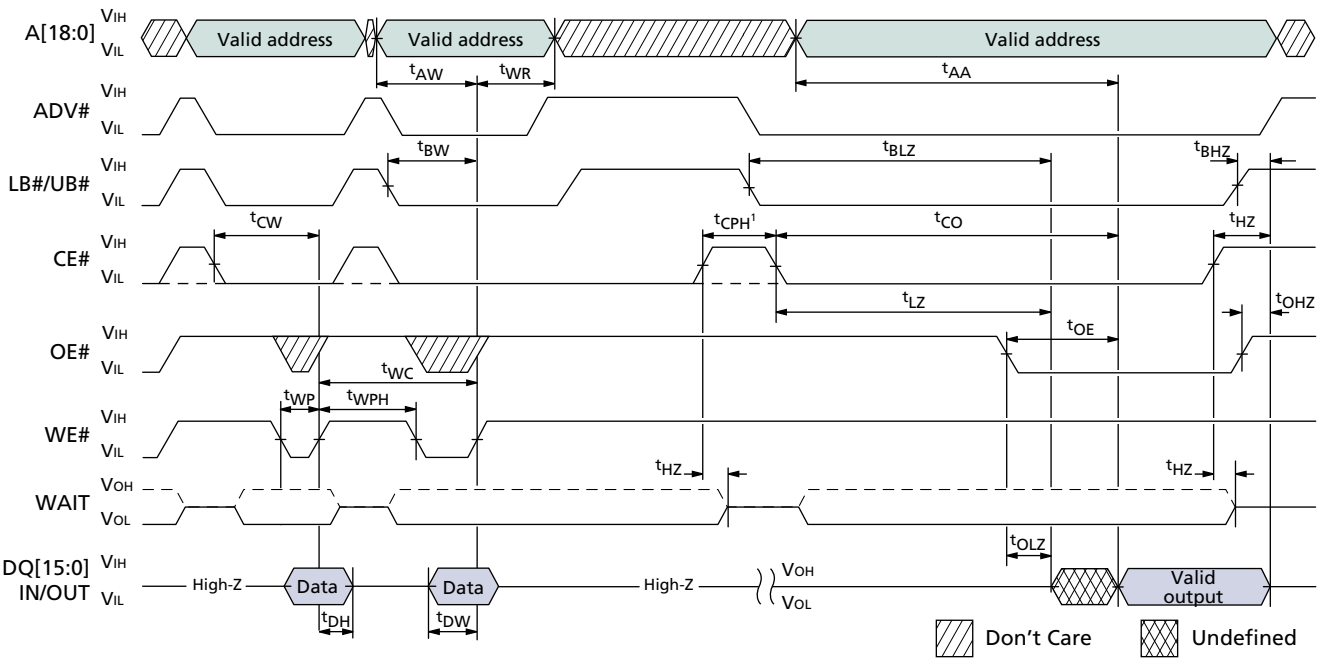
Notes: 1. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns. Note that CellularRAM Workgroup specification 1.0 requires CE# to be clocked HIGH to terminate the burst.

Figure 46: Burst READ Followed by Asynchronous WRITE Using ADV#



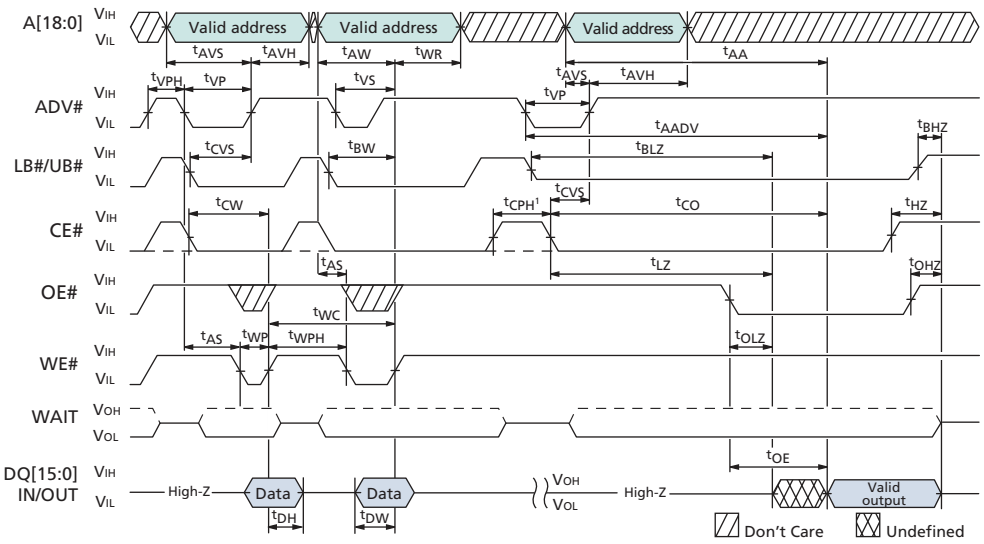
Notes: 1. When configured for synchronous mode (BCR[15] = 0), a refresh opportunity must be provided every ^{t}CEM. A refresh opportunity is satisfied by either of the following two conditions: clocked CE# HIGH or CE# HIGH for greater than 15ns. Note that CellularRAM Workgroup specification 1.0 requires CE# to be clocked HIGH to terminate the burst.

Figure 47: Asynchronous WRITE Followed by Asynchronous READ – ADV# LOW



Notes: 1. When configured for synchronous mode (BCR[15] = 0), CE# must remain HIGH for at least 5ns (^{t}CPH) to schedule the appropriate internal refresh operation. Otherwise, ^{t}CPH is only required after CE#-controlled WRITEs.

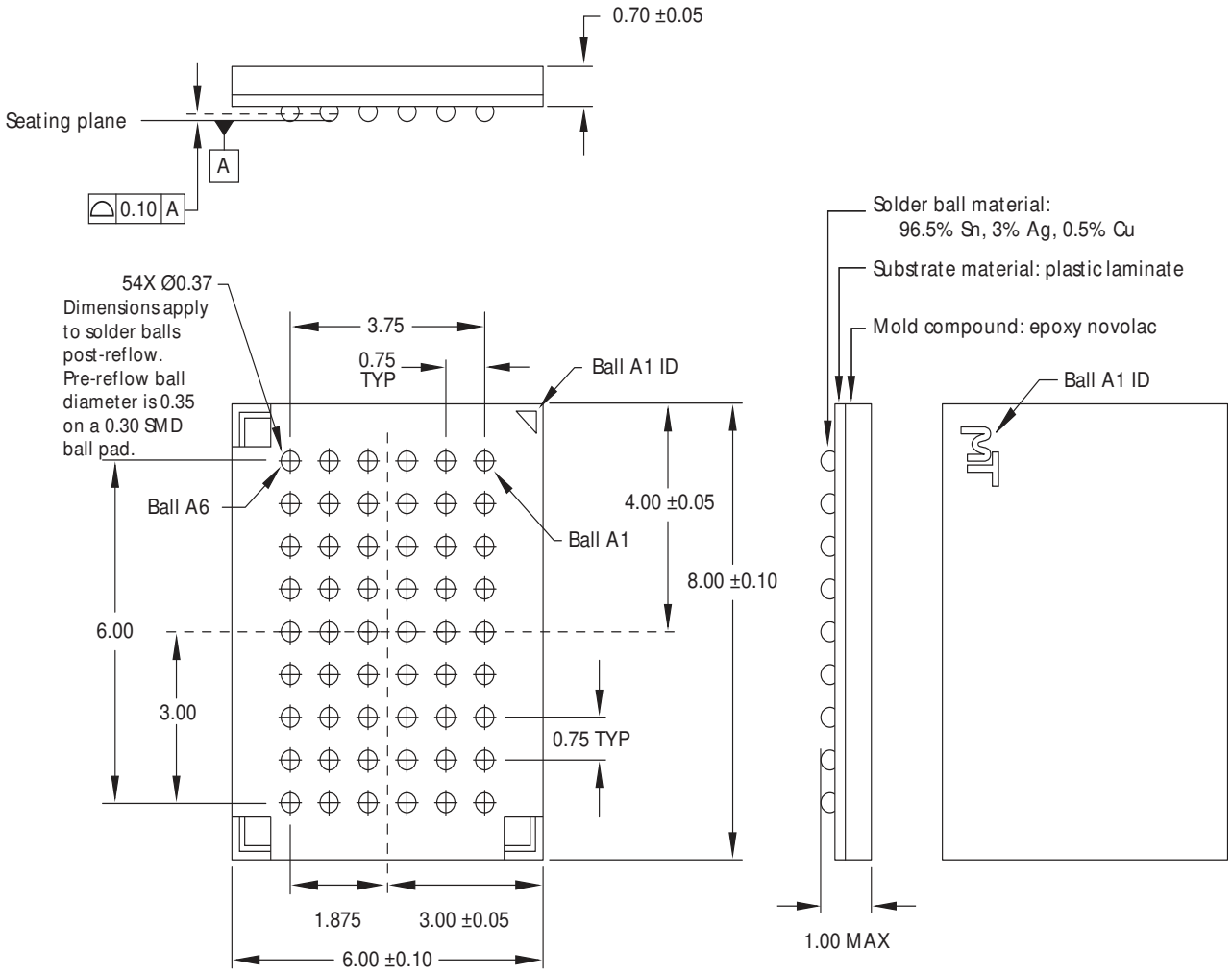
Figure 48: Asynchronous WRITE Followed by Asynchronous READ



Notes: 1. When configured for synchronous mode (BCR[15] = 0), CE# must remain HIGH for at least 5ns (^{t}CPH) to schedule the appropriate internal refresh operation. Otherwise, ^{t}CPH is only required after CE#-controlled WRITEs.

Package Dimensions

Figure 49: 54-Ball VFBGA



Notes:
1. All dimensions are in millimeters; MAX/MIN or typical (TYP) where noted.
2. Package width and length do not include mold protrusion; allowable mold protrusion is 0.25mm per side.
3. The MT45W512KW16BEGB uses "green" packaging.

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Revision History

Rev. C, Production 4/08

- Changed to production status.

Rev. B, Preliminary 3/08

- "Options" on page 1, "Part Number Chart" on page 9, Table 7, "Electrical Characteristics and Operating Conditions," on page 30: Added low-power option.
- Figure 13: "Asynchronous Mode Configuration Register Write Followed by READ ARRAY Operation," on page 18: Deleted CLK and added "(except A17)" under A[18:0].
- Figure 14: "Synchronous Mode Configuration Register WRITE Followed by READ ARRAY Operation," on page 19: Added "(except A17)" under A[18:0].
- Figure 15: "Asynchronous Mode Configuration Register READ Followed by READ ARRAY Operation," on page 20: Corrected ^{t}AAVD to ^{t}AADV.
- "Burst Length (BCR[2:0]) Default = Continuous Burst" on page 25, and "Burst Wrap (BCR[3]) Default = Burst No Wrap (Within Burst Length)" on page 25: Corrected internal address wrap to 00000h.
- Figure 32: "Single-Access Burst READ Operation," on page 40, Figure 33: "Four-Word Burst READ Operation," on page 41, Figure 34: "READ Burst Suspend," on page 42, Figure 42: "Burst WRITE Followed by Burst READ," on page 50: Corrected timing paramter for LB#/UB# flling to CLK rising to ^{t}SP.

Rev. A, Preliminary 11/07

- Initial release.